

Introduction to μ SR Muon Spin Rotation/Relaxation

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- The polarized muon as a magnetic micro-probe
- Generation of polarized muon beams
- Time evolution of muon spin polarization: depolarization and relaxation
- Some typical examples
- Magnetism
- Superconductivity
- Studies in thin films, heterostructures
- Not treated: many things: Muonium (semiconductors), level crossing techniques (chemistry, soft matter), dynamical and critical phenomena (magnetism), resonance...

<http://people.web.psi.ch/morenzoni>

Script of lecture ETH-Z/Uni ZH: Physics with muons

BOOKS

- A. Yaouanc, P. Dalmas de Réotier, MUON SPIN ROTATION, RELAXATION and RESONANCE (Oxford University Press, 2010)
- A. Schenck, MUON SPIN ROTATION SPECTROSCOPY, (Adam Hilger, Bristol 1985)
- E. Karlsson, SOLID STATE PHENOMENA, As Seen by Muons, Protons, and Excited Nuclei, (Clarendon, Oxford 1995)
- S.L. Lee, S.H. Kilcoyne, R. Cywinski eds, MUON SCIENCE: MUONS IN PHYSICS; CHEMISTRY AND MATERIALS, (IOP Publishing, Bristol and Philadelphia, 1999)

Literature

INTRODUCTORY ARTICLES

- S.J. Blundell, SPIN-POLARIZED MUONS IN CONDENSED MATTER PHYSICS, Contemporary Physics 40, 175 (1999)
- P. Bakule, E. Morenzoni, GENERATION AND APPLICATIONN OF SLOW POLARIZED MUONS, Contemporary Physics 45, 203-225 (2004).

REVIEW ARTICLES, APPLICATIONS

- P. Dalmas de Réotier and A. Yaouanc, MUON SPIN ROTATION AND RELAXATION IN MAGNETIC MATERIALS, J. Phys. Condens. Matter 9 (1997) pp. 9113-9166
- A. Schenck and F.N. Gygax, MAGNETIC MATERIALS STUDIED BY MUON SPIN ROTATION SPECTROSCOPY, In: Handbook of Magnetic Materials, edited by K.H.J. Buschow, Vol. 9 (Elsevier, Amsterdam 1995) pp. 57-302
- B.D. Patterson, MUONIUM STATES IN SEMICONDUCTORS, Rev. Mod. Phys. 60 (1988) pp. 69-159
- A. Amato, HEAVY-FERMION SYSTEMS STUDIED BY μ SR TECHNIQUES, Rev. Mod. Phys., 69, 1119 (1997)
- V. Storchak, N. Prokovev, QUANTUM DIFFUSION OF MUONS AND MUONIUM ATOMS IN SOLIDS, Rev. Mod. Physics, 70, 929 (1998)
- J. Sonier, J. Brewer, R. Kiefl, μ SR STUDIES OF VORTEX STATE IN TYPE-II SUPERCONDUCTORS, Rev. Mod. Physics, 72, 769 (2000)
- E. Roduner, THE POSITIVE MUON AS A PROBE IN FREE RADICAL CHEMISTRY, Lecture Notes in Chemistry No. 49 (Springer Verlag, Berlin 1988)

Muon properties

Properties of polarized (positive) muons make them sensitive magnetic microprobes of matter.

Mass:

$$m_\mu = 105.658 \text{ MeV/c}^2 \approx 207 m_e \approx 1/9 m_p$$

Charge:

$$+e, (-e)$$

interstitial position (generally),
local probe

Spin :

$$s = 1/2$$

Magnetic moment:

$$\mu_\mu = g_\mu \frac{e\hbar}{2m_\mu} s$$

$$(g_\mu \approx 2.001165\ 920\ 69\ (60))$$

$$\mu_\mu = 3.18 \mu_p$$

very sensitive magnetic probe
 10^{-3} - $10^{-4} \mu_B$
(no quadrupolar effects)

Gyromagnetic ratio:

$$\gamma_\mu = \frac{\mu_\mu}{\hbar s} = g_\mu \frac{e}{2m_\mu}$$

$$851.615 \text{ MHz/T}$$

Life time:

$$\tau_\mu = 2.19714 \mu\text{s}$$

Fluctuation time window
 $10^{-5} < t < 10^{-11} \text{ s}$

Bound state:

$$\mu^+ e^-$$

Muonium, H-Isotop

μ SR: Muon Spin Rotation/Relaxation

Method:

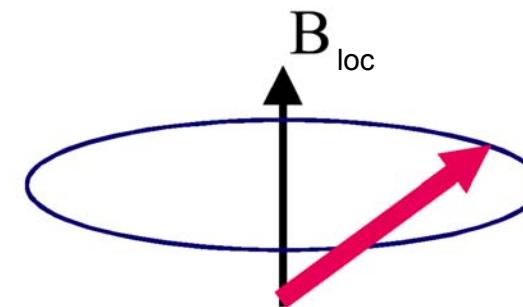
- Implant and thermalize ~100% polarized muons in matter (stopping time in solid ~ 10 ps, no initial loss of polarization, stop site: generally interstitial).

$$P(0) \approx 1$$

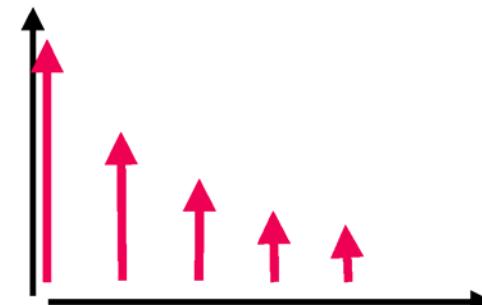
- Magnetic moment of muon interacts with local magnetic fields (moments, currents, spins) $\rightarrow P(t)$
- $P(t)$ is characterized by precession and/or depolarization/relaxation.
- Observe time evolution of the polarization $P(t)$ of the muon ensemble via asymmetric muon decay: (positrons preferentially emitted along muon spin).
- $P(t)$ contains information about static and dynamic properties of local environment (fields, moments,...)

$$\frac{d\vec{\mu}_\mu}{dt} = \gamma_\mu (\vec{\mu}_\mu \times \vec{B}(t)) \quad \vec{P} = \frac{<\vec{s}>}{\frac{1}{2}\hbar}$$

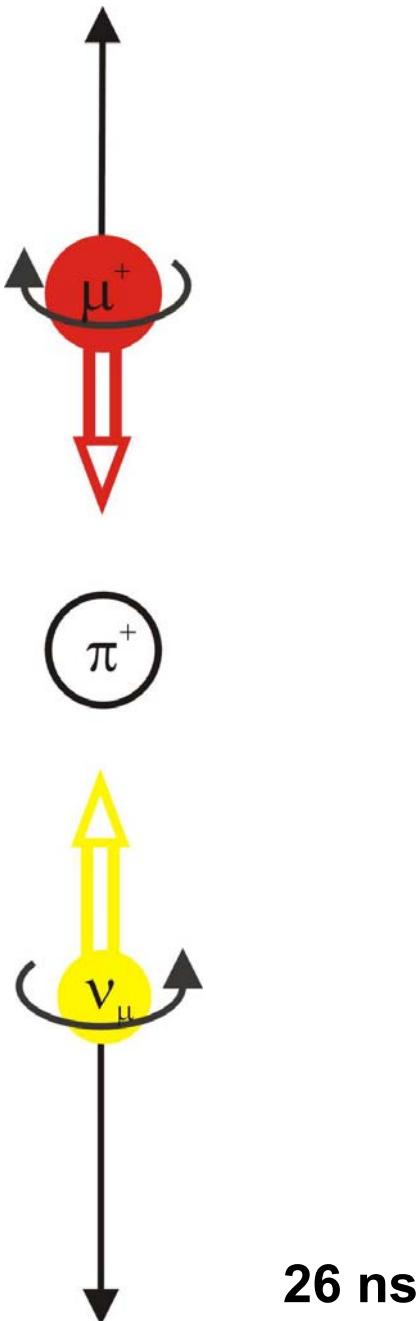
$$\frac{d\vec{P}}{dt} = \gamma_\mu (\vec{P} \times \vec{B}(t))$$



$$\omega_L = \gamma_\mu B_{loc}$$



Production of polarized muons



Parity violation in pion decay allows production of polarized muon beams.

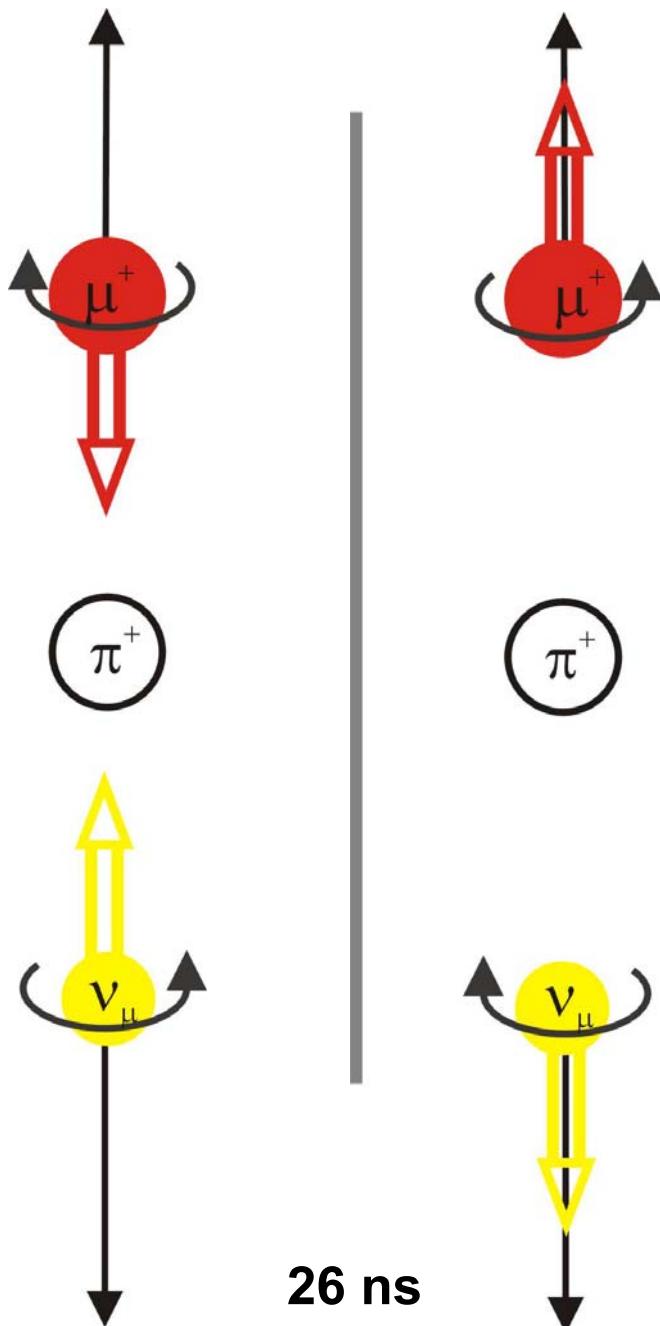
Only “left handed” neutrinos →
in pion rest frame muon spin antiparallel to momentum.

Kinematics of pion decay at rest;
from energy and momentum conservation:

Momentum: $p_\mu = 29.79 \text{ MeV/c}$

Kinetic energy: $E_\mu = 4.12 \text{ MeV}$

Production of polarized muons



Parity violation in pion decay allows production of polarized muon beams.

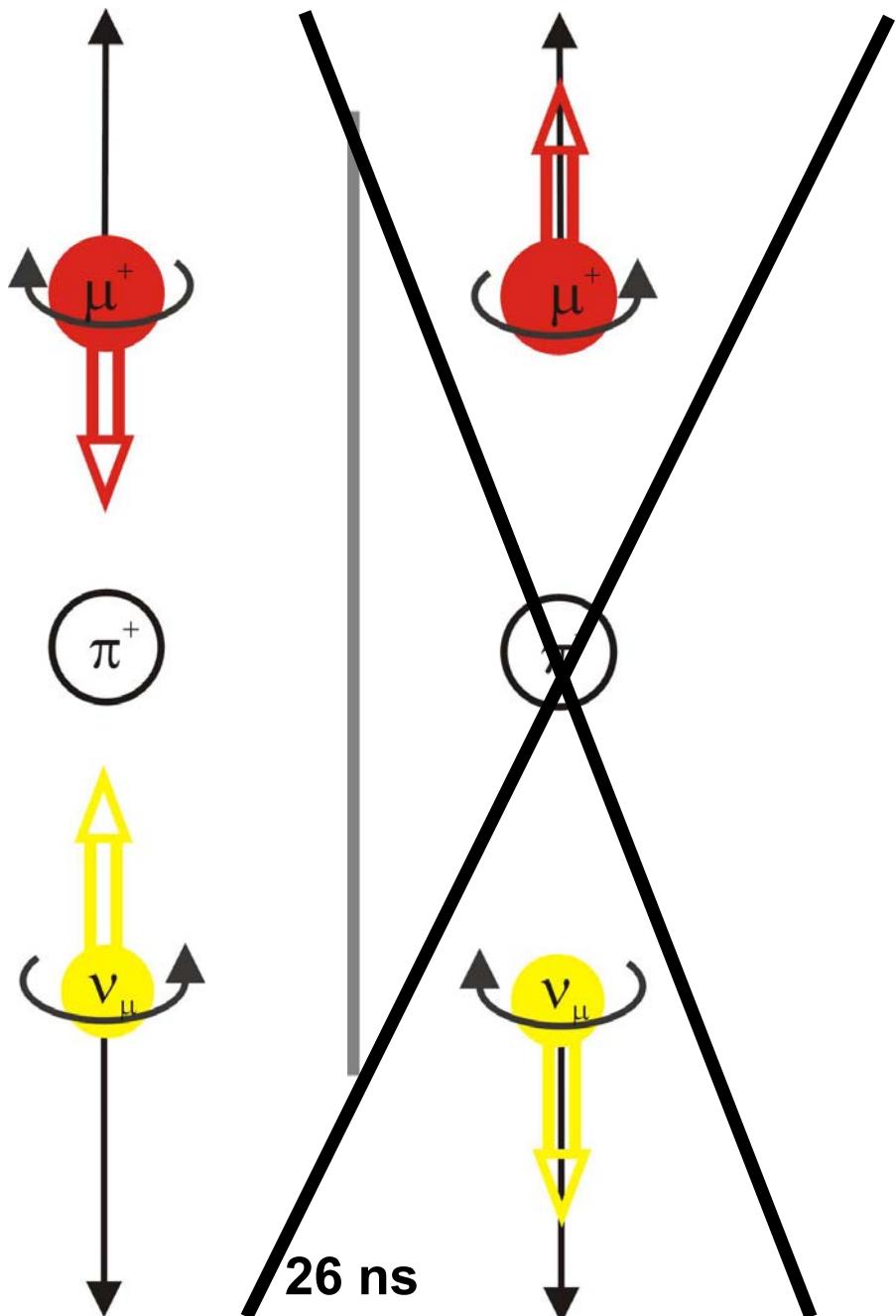
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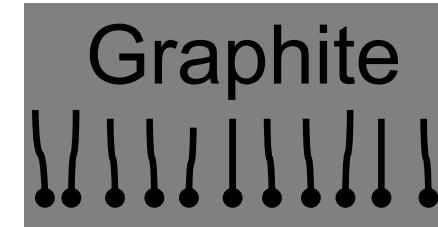
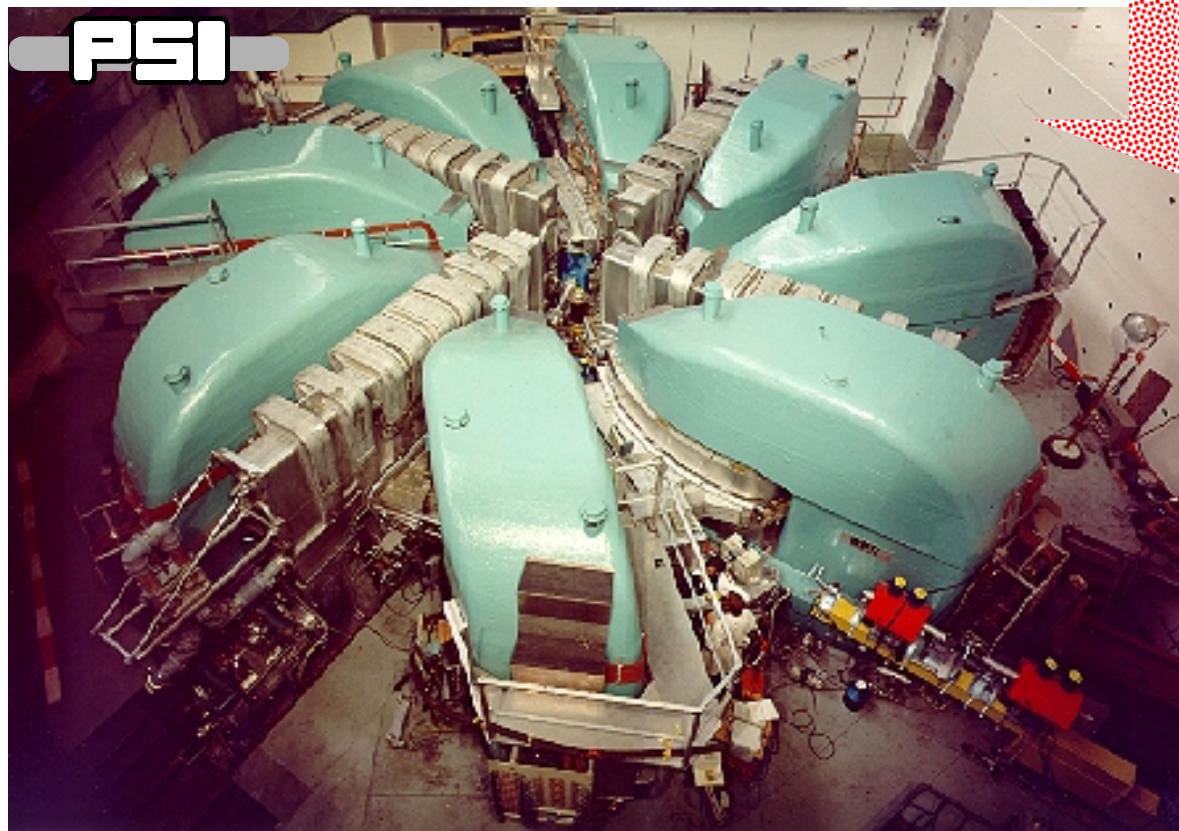
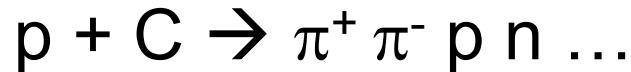
Momentum: $p_\mu = 29.79 \text{ MeV/c}$

Kinetic energy: $E_\mu = 4.12 \text{ MeV}$

Generation of polarized muons (μ^+)

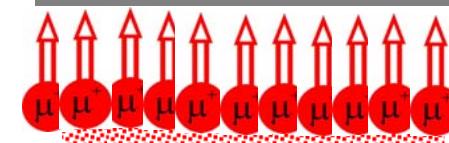
2.2 mA $\approx 1.4 \cdot 10^{16}$ Protons/sec

with 600 MeV



Production Target

$\leftarrow \pi^+$



„Surface“
muons

μ^+

$\sim 10^7 - 10^8 \mu^+/\text{sec}$

100 % pol.

$\sim 4 \text{ MeV}$

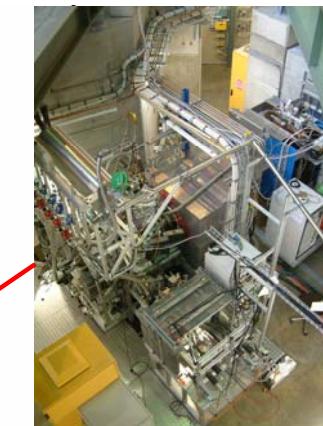
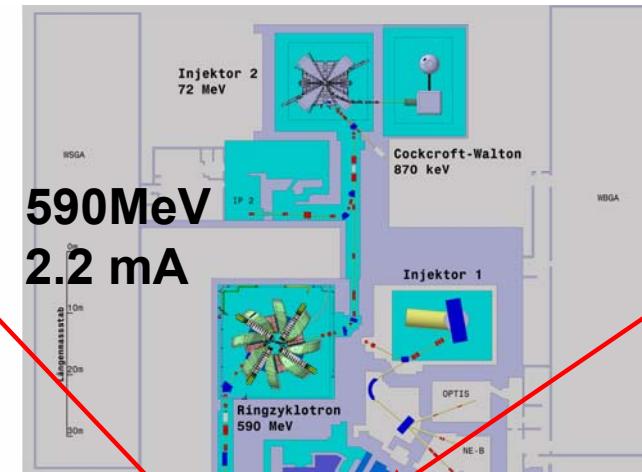
generally used for “bulk”
condensed matter studies

For thin film studies: eV-30 keV

S μ S: The Swiss Muon Source

High Field μ SR, 9.5 T, 20 mK

Until 2011 Avoided
Level crossings
instrument ALC



LEM

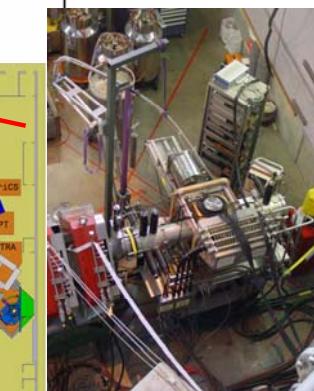
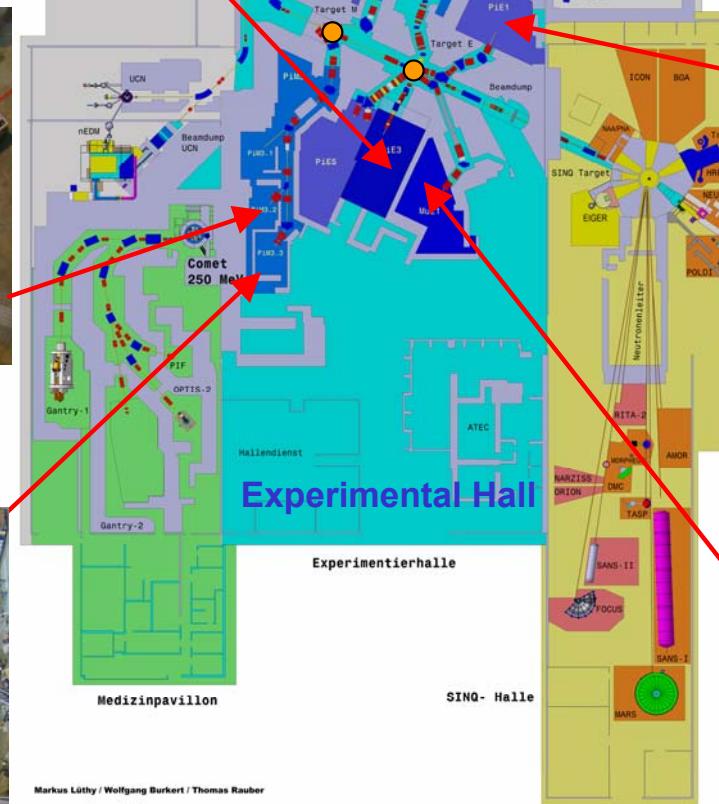
Low-energy muon beam and instrument, tunable energy (**0.5-30 keV**, μ^+), thin-film, near-surface and multi-layer studies (1-300 nm)

**0.3 T,
2.5 K**

GPS

General Purpose Surface
Muon Instrument
Muon energy: **4.2 MeV** (μ^+)

0.6 T, 1.8 K



DOLLY

General Purpose
Surface Muon Instrument
Muon energy: **4.2 MeV** (μ^+)

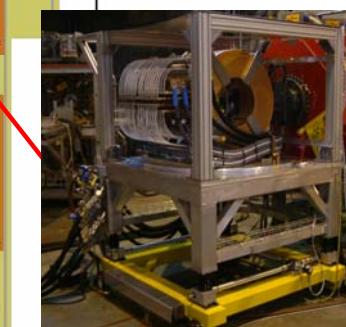
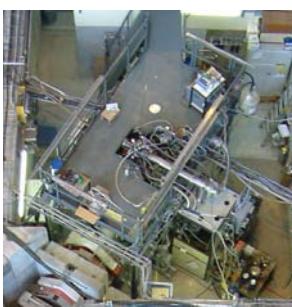
**0.5 T
2 K (0.25K)**

Shared Beam Surface Muon Facility (Muon On REquest)

LTF

Low Temperature Facility
Muon energy: **4.2 MeV** (μ^+)

**3 T,
20 mK- 4 K**



GPD

General Purpose Decay
Channel Instrument
Muon energy: **5 - 60 MeV**
(μ^+ or μ^-)

**0.5 T,
300 mK
2.8 GPa**

Measuring P(t): Muon Decay $\mu^+ \rightarrow e^+ + \bar{\nu}_\mu + \nu_e$

- Muon decay (life time 2.2. μ s) violates parity conservation
→ asymmetric decay
- Positrons preferentially emitted along muon spin (along polarization vector of muon ensemble)

$$\frac{dN_{e^+}(\theta)}{d\Omega} \propto \left(1 + \frac{1}{3} P \cos \theta\right) = \left(1 + \frac{1}{3} \vec{P} \cdot \vec{n}\right)$$

\vec{n} : direction of observation (detector position)

- Measuring positrons allows to observe time evolution of the polarization $P(t)$ of the muon ensemble
- Positron intensity as a function of time after implantation:

$$N_{e^+}(t) = N_0 \left[1 + A_0 P(t)\right] e^{-\frac{t}{\tau_\mu}} \quad P(t) = \vec{P}(t) \cdot \vec{n}$$

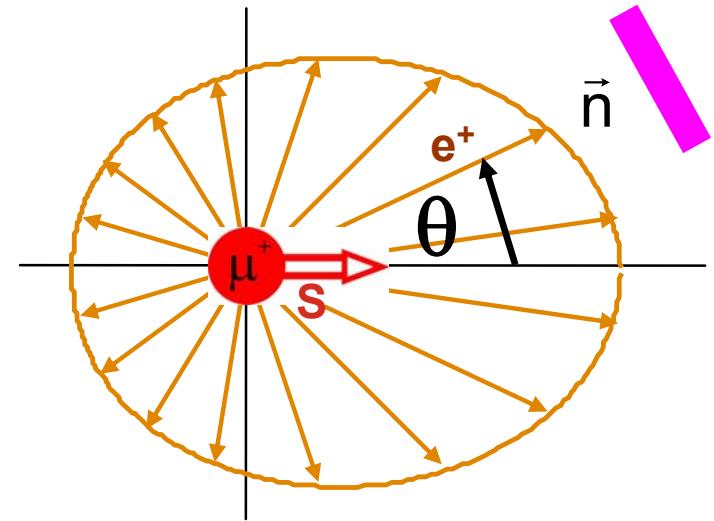
- A_0 : Maximum observable asymmetry

theoretically: $A_0 = 1/3$

practically it depends on setup (average over solid angle, absorption in materials): $A_0 = 0.25 - 0.30$

- $A_0 P(t)$ is called asymmetry: $A(t)$

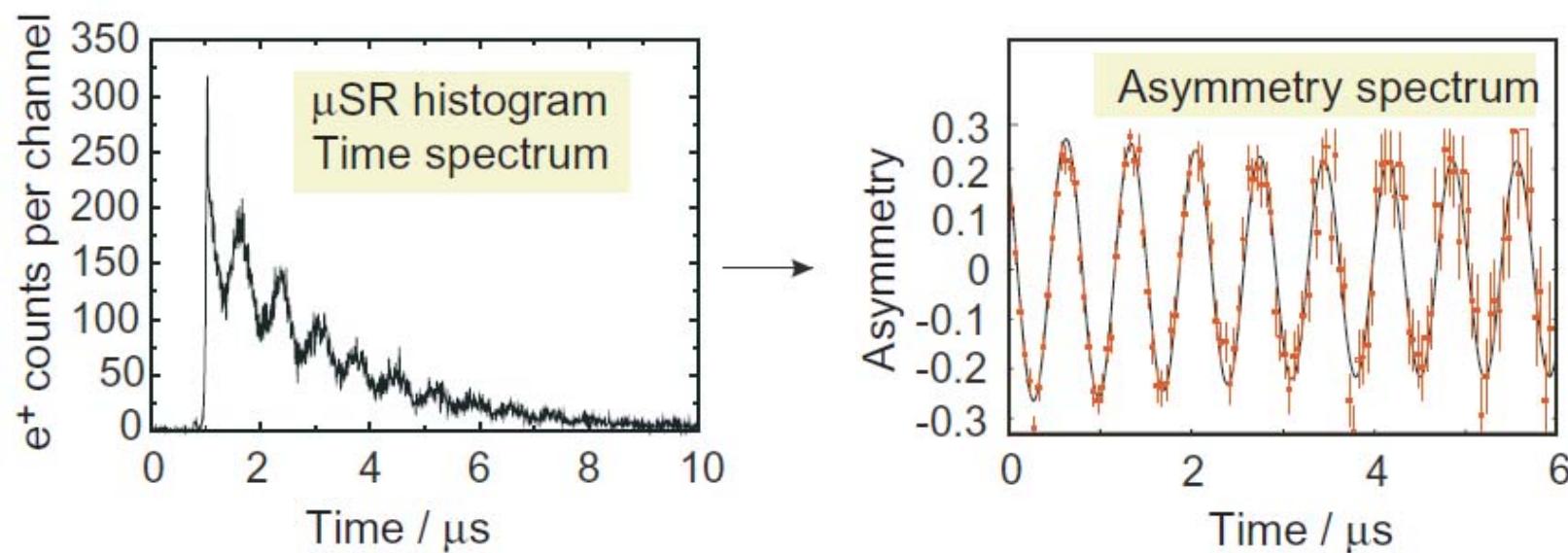
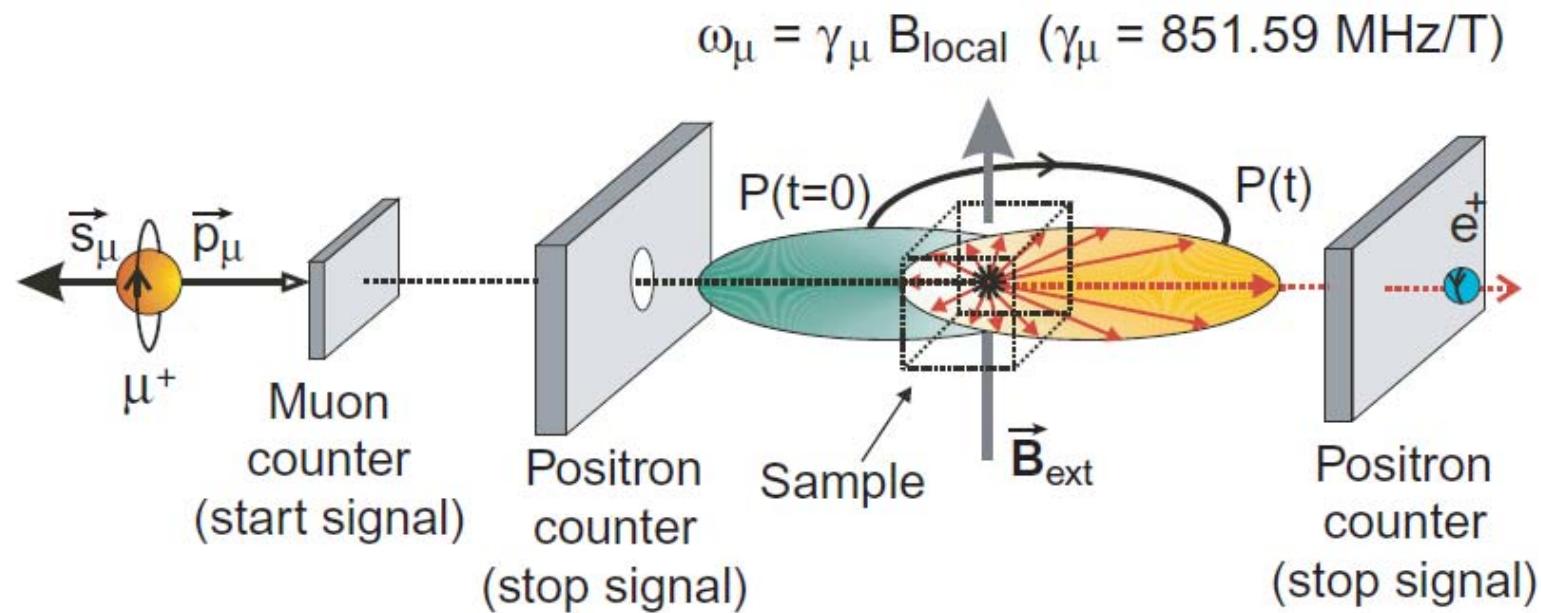
For $P=1$:



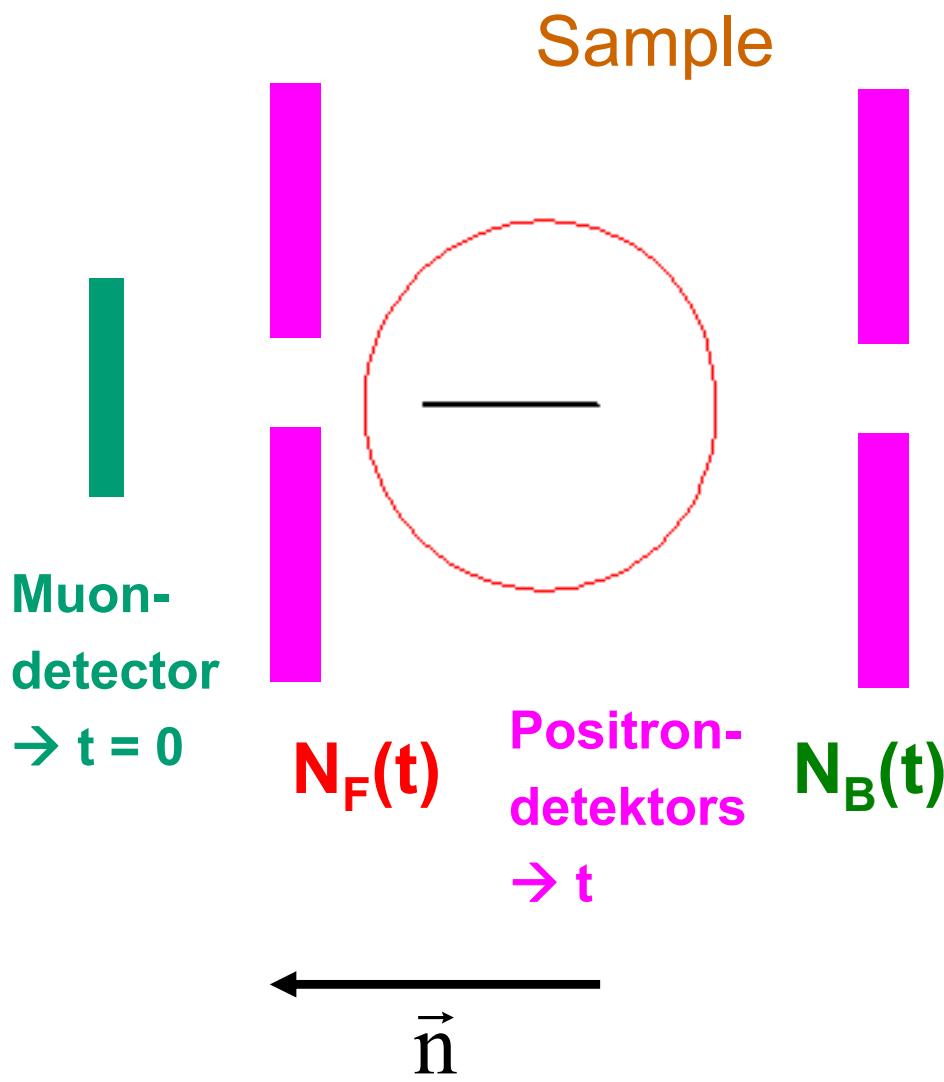
$$\frac{dN_{e^+}(\theta)}{d\Omega} \propto \left(1 + \frac{1}{3} P \cos \theta\right)$$

θ : angle between spin (polarization) and positron direction

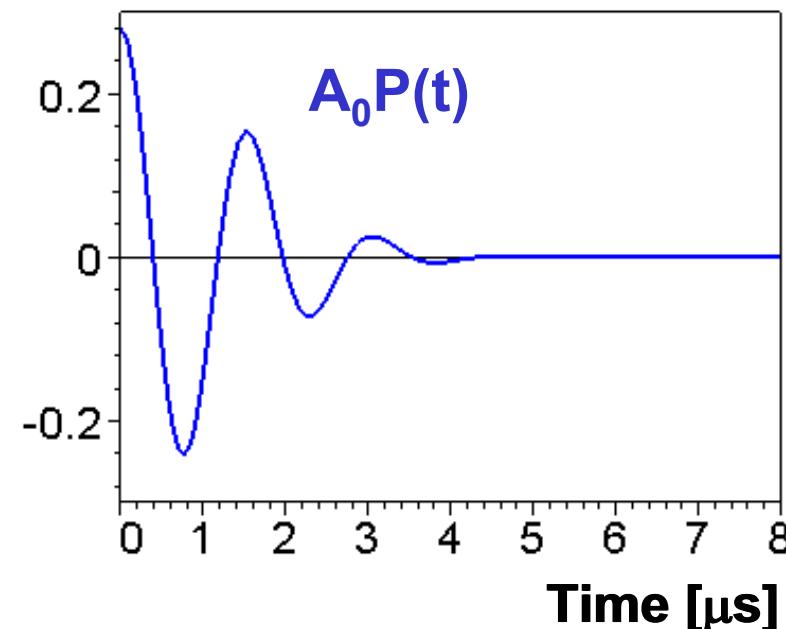
Principle of a μ SR experiment

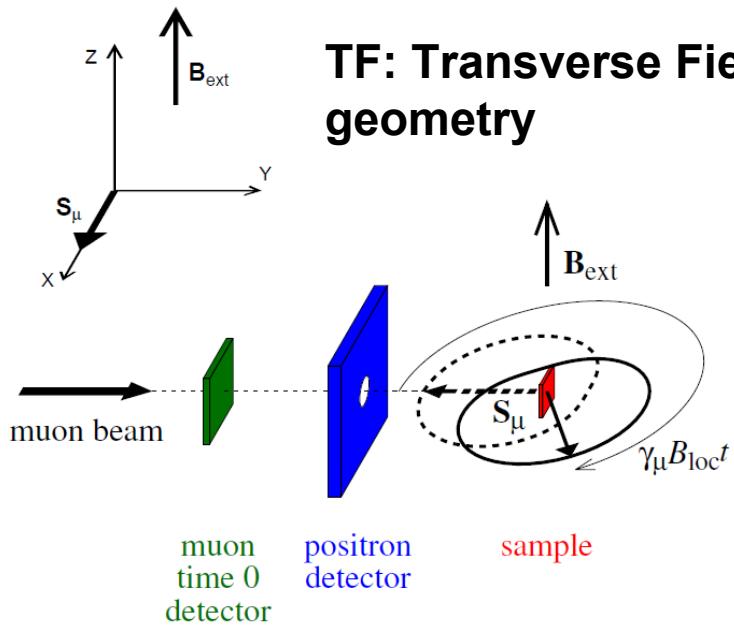


μ SR: Muon Spin Rotation/Relaxation

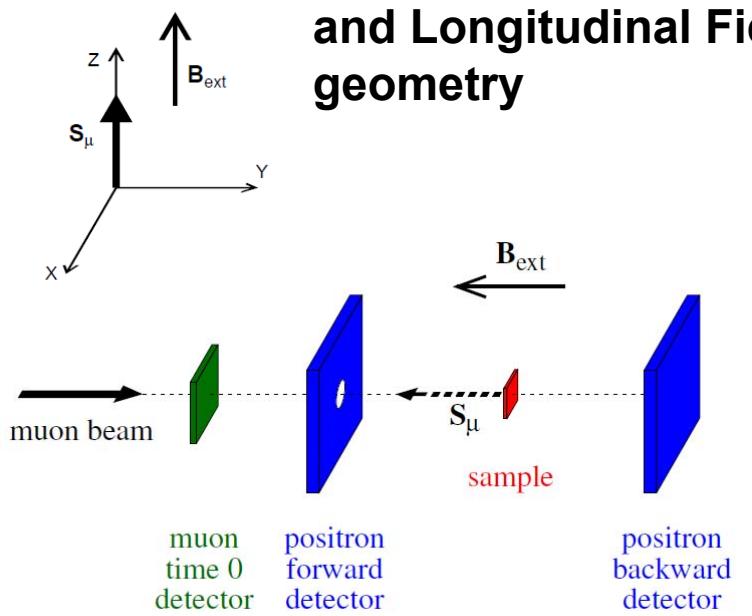
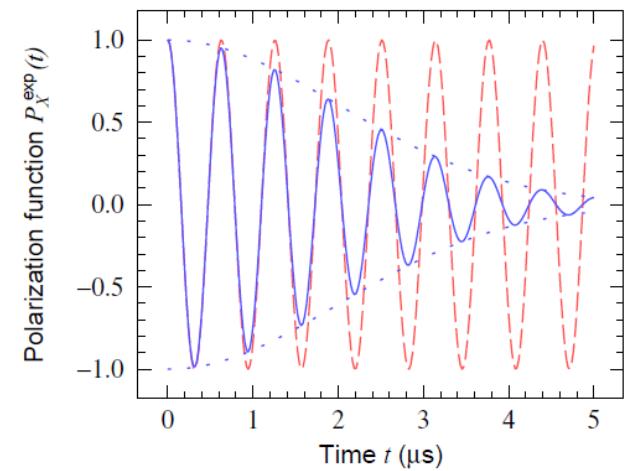
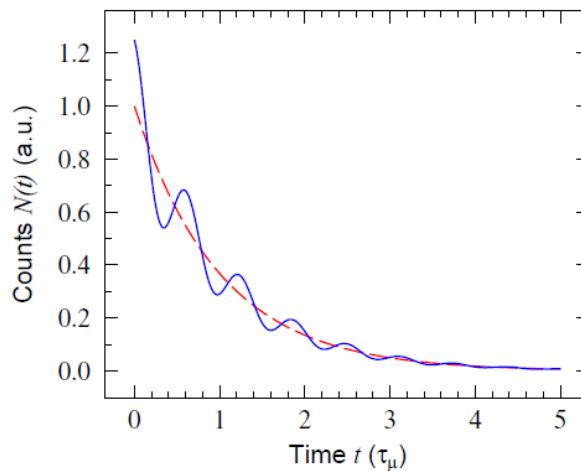


$$N_F(t) = N_0 \left[1 + A_0 \vec{P}(t) \cdot \vec{n} \right] e^{-\frac{t}{\tau_\mu}}$$
$$N_B(t) = N_0 \left[1 - A_0 \vec{P}(t) \cdot \vec{n} \right] e^{-\frac{t}{\tau_\mu}}$$
$$\frac{N_F(t) - N_B(t)}{N_F(t) + N_B(t)} = AP(t) \quad (P(t) = \vec{P}(t) \cdot \vec{n})$$

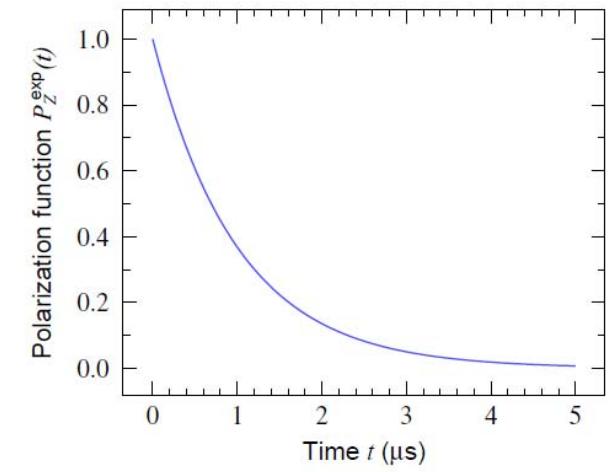
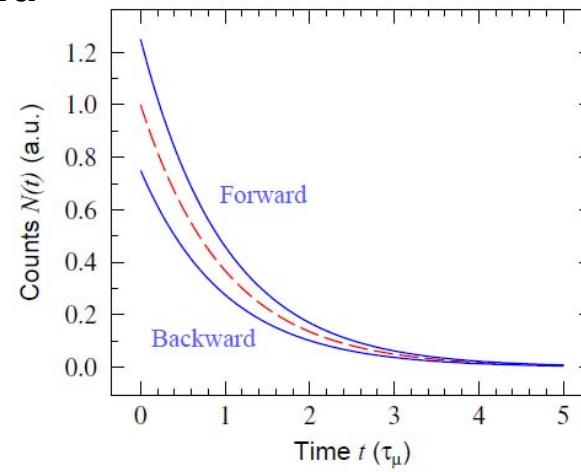




TF: Transverse Field geometry



ZF and LF: Zero field and Longitudinal Field geometry



P(t): time evolution of polarization

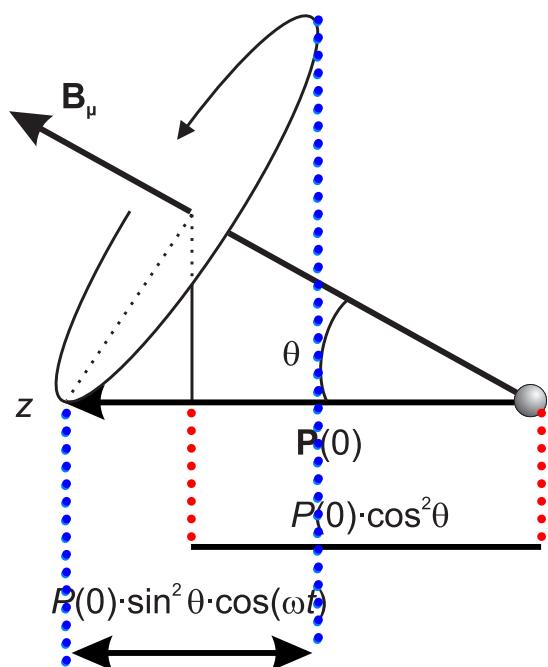
$$\frac{d\vec{P}}{dt} = \gamma_\mu (\vec{P} \times \vec{B}(t))$$

\vec{B} is the total field at muon site (i.e. including applied field)

Simplest case:

All muons in the sample experience the same static field $\vec{B} = (B_x, B_y, B_z)$

Static means: \vec{B} does not change over observation time (5-10 τ_μ): $\frac{\vec{B}(t)}{dB(t)/dt} \gg \tau_\mu$



$\vec{P}(0) \parallel \hat{z} \equiv \hat{n}$ (Direction of observation)

$$P_B(t) = \cos^2 \theta + \sin^2 \theta \cos(\omega_L t) = \frac{B_z^2}{B^2} + \frac{B_x^2 + B_y^2}{B^2} \cos(\gamma_\mu B t)$$

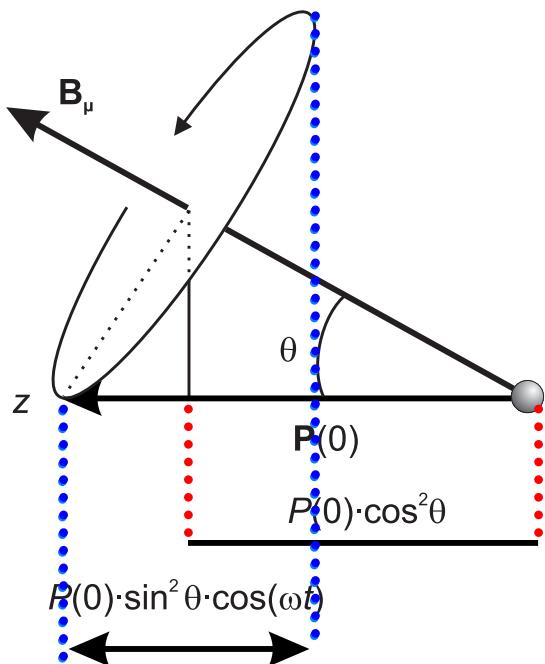
$\omega_L \equiv \gamma_\mu B$ Larmor Frequency (Spin precession frequency)

P(t): time evolution of polarization

$$\frac{d\vec{P}}{dt} = \gamma_\mu (\vec{P} \times \vec{B}(t))$$

\vec{B} is the total field at muon site (i.e. including applied field)

In case the muons experience a field distribution $p(\vec{B})$

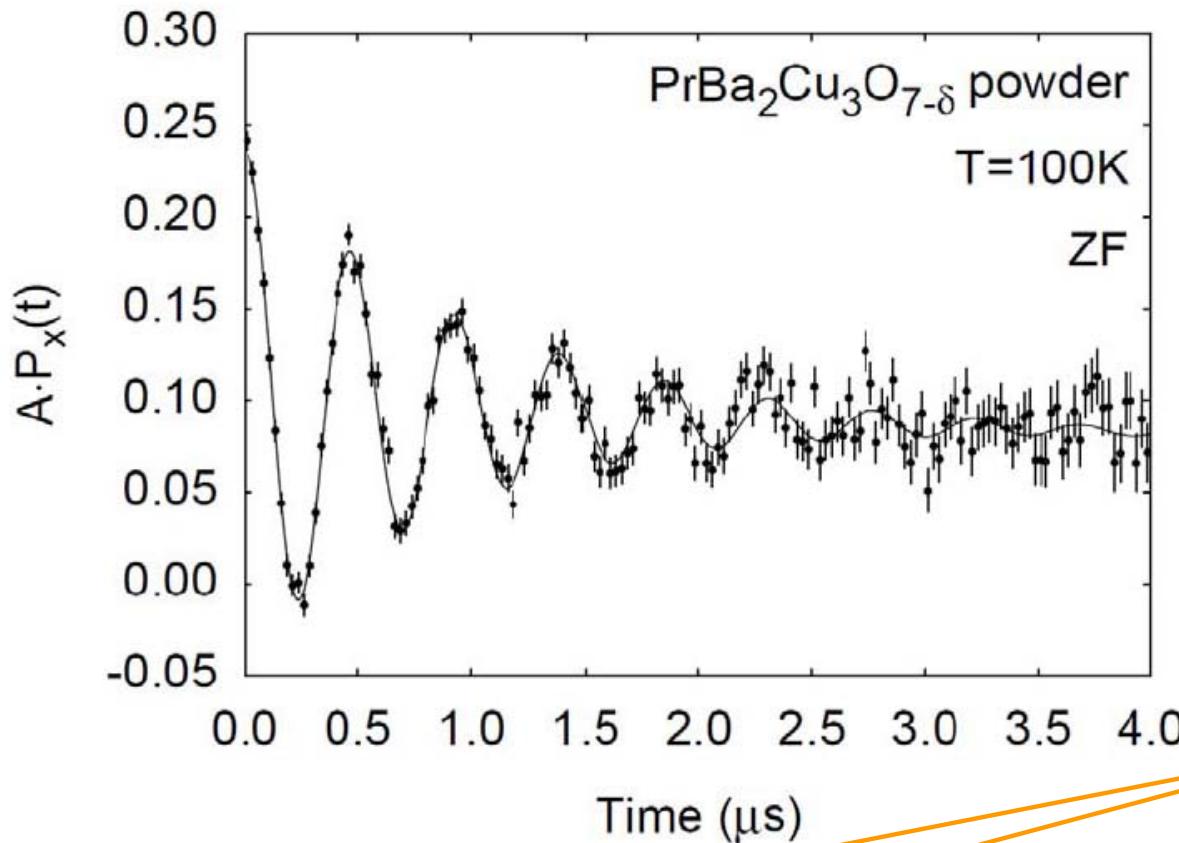


$$P(t) = \int p(\vec{B}) P_{\vec{B}}(t) d^3B = \int p(\vec{B}) \left[\frac{B_z^2}{B^2} + \frac{B_x^2 + B_y^2}{B^2} \cos(\gamma_\mu B t) \right] d^3B$$

Magnetism: polycrystalline sample

$|\vec{B}|$ equal all over the sample, isotropic direction:

$$P(t) = \frac{1}{4\pi} \int \cos^2 \theta + \sin^2 \theta \cos(\gamma_\mu |\vec{B}| t) d\phi \, d(\cos \theta) = \frac{1}{3} + \frac{2}{3} \cos(\gamma_\mu |\vec{B}| t)$$

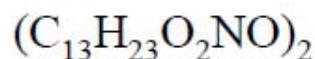


Damping,
Depolarization

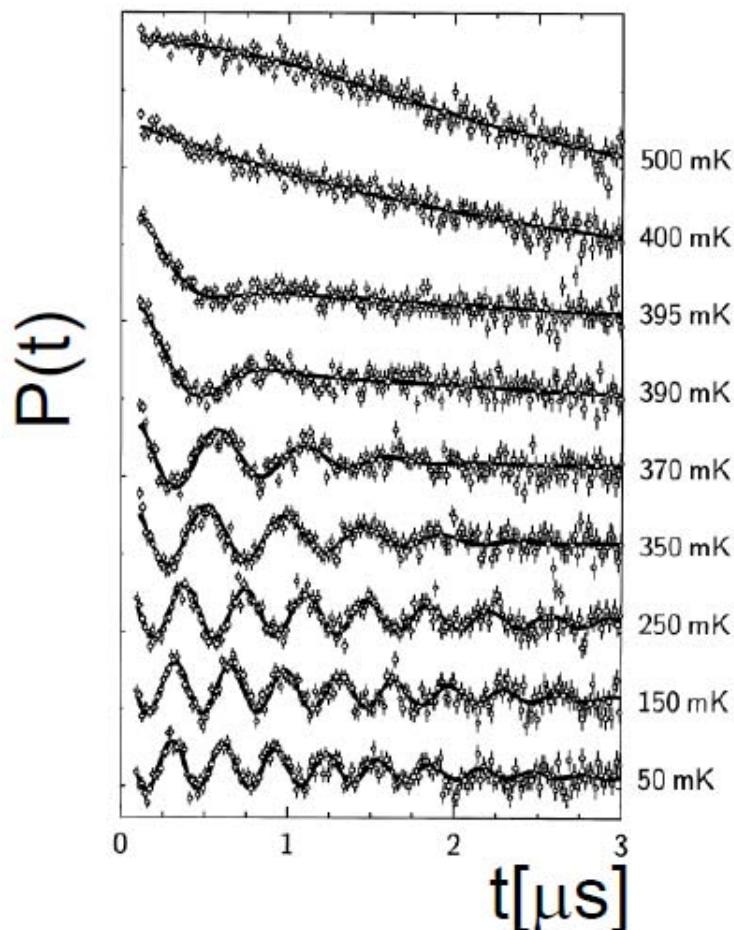
$$A_0 P(t) = A_0 \left[e^{-\lambda_L t} \frac{1}{3} + e^{-\lambda_T t} \frac{2}{3} \cos(\gamma_\mu |\vec{B}| t) \right]$$

Microscopic magnetometry

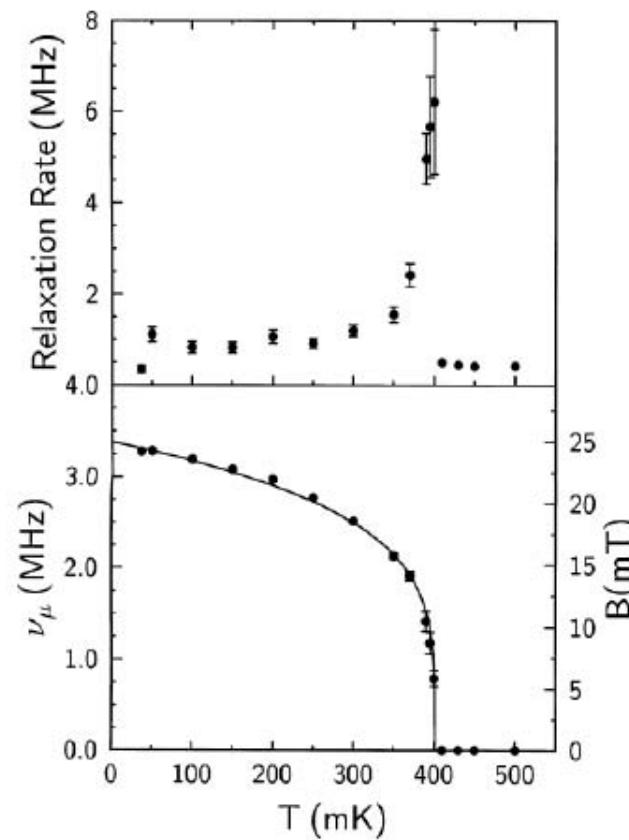
$B_{\text{ext}} = 0$



Organic antiferromagnet



S. Blundell et al., Physica B (2000)



$$P(t) = a_L(t) + a_T e^{-\lambda t} \cos(2\pi\nu_\mu t)$$
$$\lambda = \frac{1}{T} \quad \text{relaxation rate, } [\mu\text{s}^{-1}] \text{ or [MHz]}$$

Local field in magnetic materials

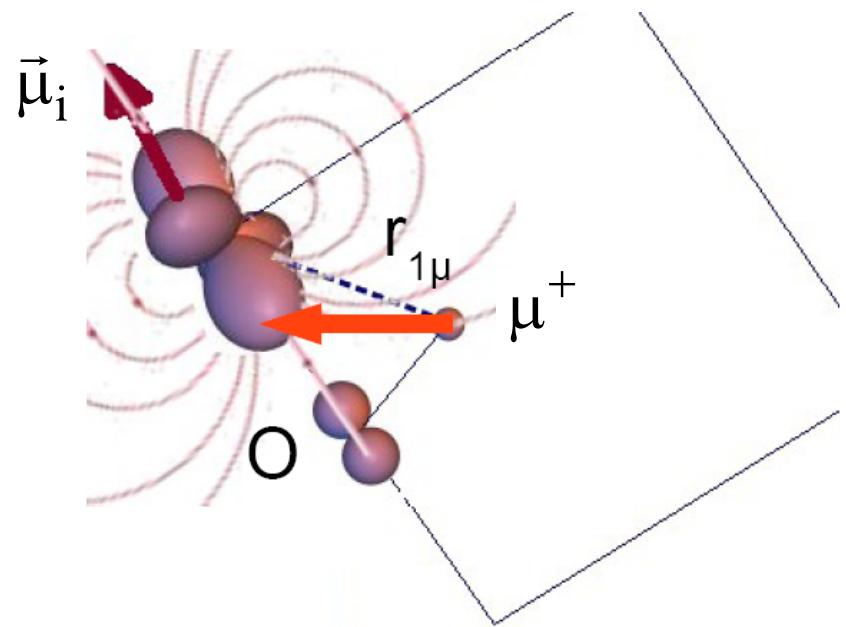
Internal field : generally sum of dipolar :

$$\vec{B}_{\text{dip}}(\vec{r}) = \frac{\mu_0}{4\pi} \frac{3(\vec{\mu}_i \cdot \vec{r}_{l\mu}) \cdot \vec{r}_{l\mu} - \vec{\mu}_i r_{l\mu}^2}{r_{l\mu}^5}$$

$$B_{\text{dip}} \approx \frac{\mu_0}{4\pi} \frac{\mu_i}{r_{l\mu}^3} \approx \frac{\mu_i [\mu_B]}{d^3 [A^3]} \quad T \approx 0.1T$$

and contact field (spin density at muon site) :

$$\vec{B}_{\text{hf}}(\vec{r}_\mu) = \frac{2\mu_0}{3} \mu_B \rho_{\text{spin}}(\vec{r}_\mu) \equiv \frac{2\mu_0}{3} \mu_B |\phi(\vec{r}_\mu)|^2 \langle \vec{s} \rangle$$



High sensitivity:

μSR time window 10-20 μs

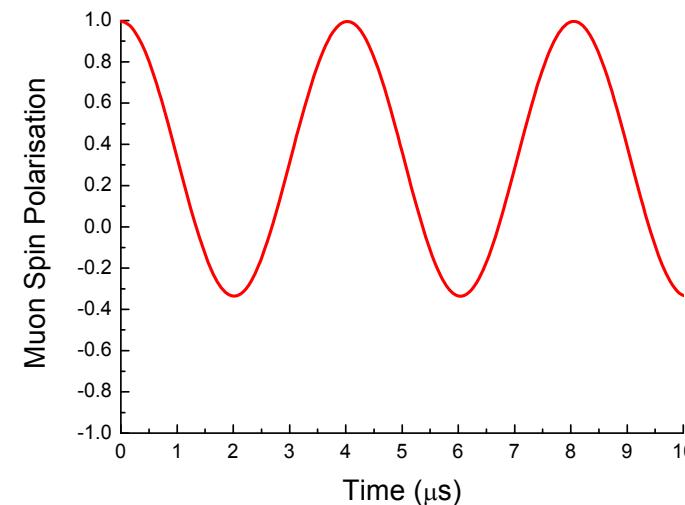
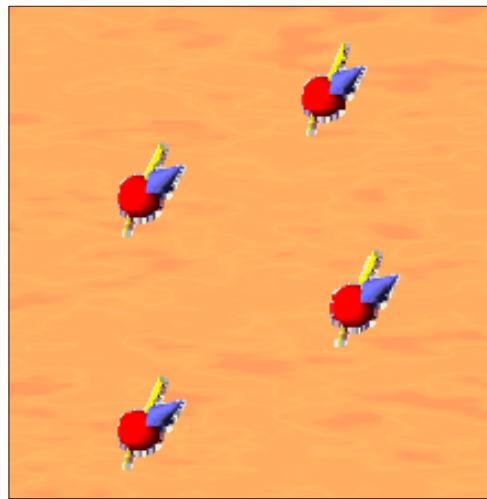
→ ν_μ ≈ 50 kHz detectable

→ B = $\frac{2\pi}{\gamma_\mu} \nu_\mu \approx 0.1 \text{ mT}$ (Gauss)

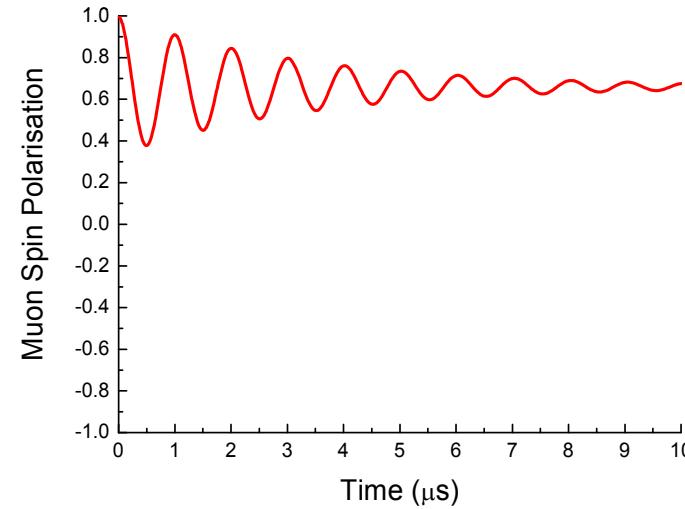
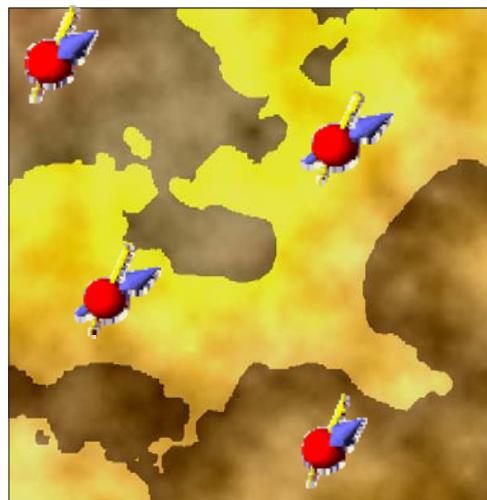
(corresponds to 0.001 μ_B or nuclear moments μ_n)

Inhomogeneous materials: determination of volume fraction

Homogeneous:



Inhomogeneous:



Amplitude a = Magnetic volume fraction

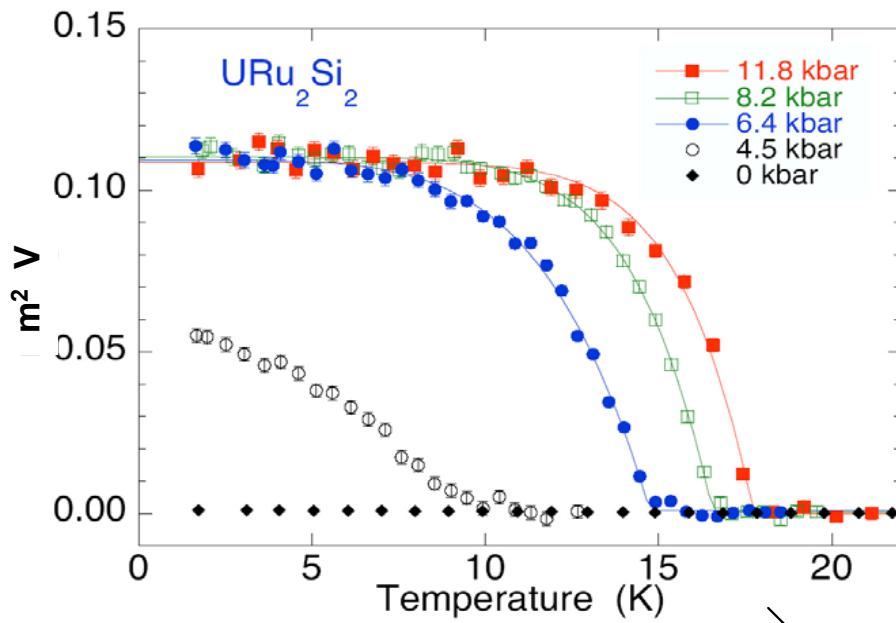
Frequency ω = Local field, size of magnetic moments

Damping λ, σ = inhomogeneity of magnetic regions

Example URu_2Si_2

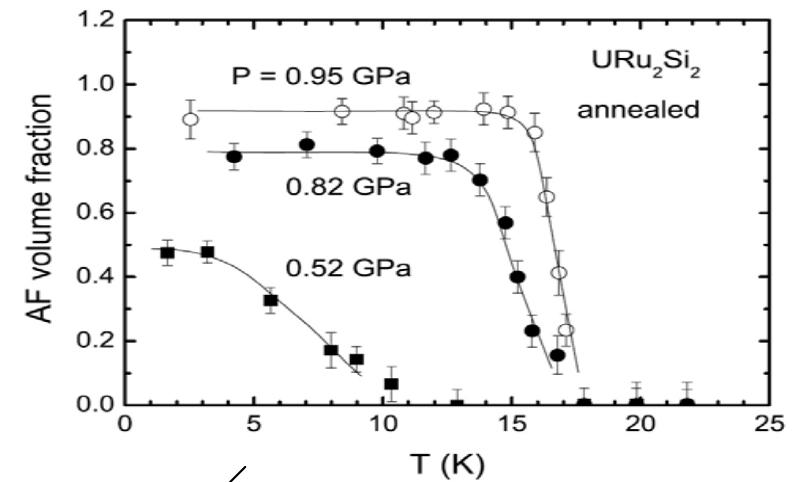
Neutron scattering:

F. Bourdarot et al., condmat/0312206



Muon Spin Rotation:

A. Amato et al., J. Phys.: Condens. Matter **16** (2004) S4403

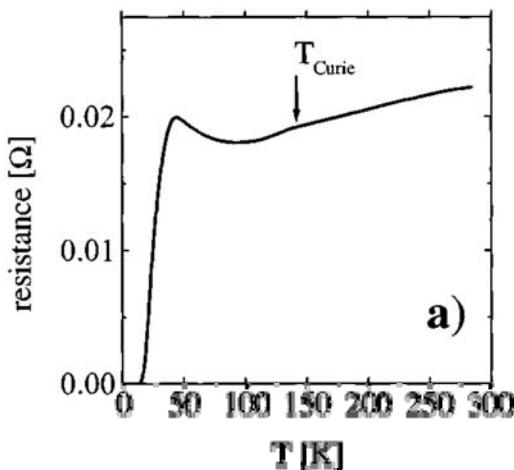


Phase separation in magnetic and non magnetic volumes

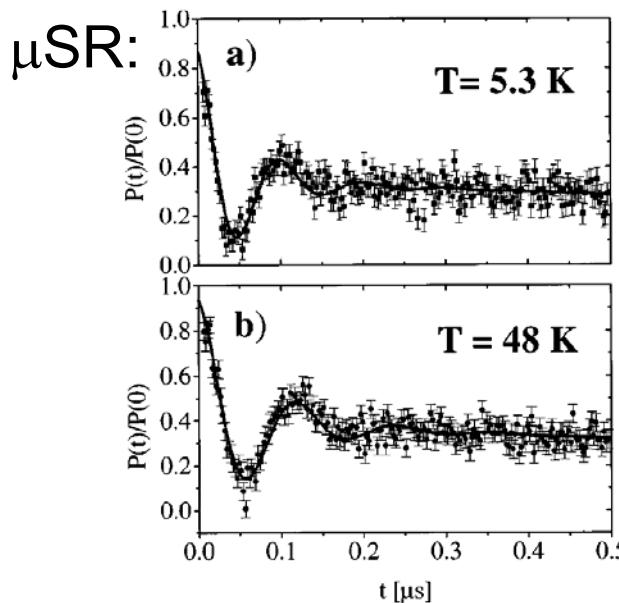
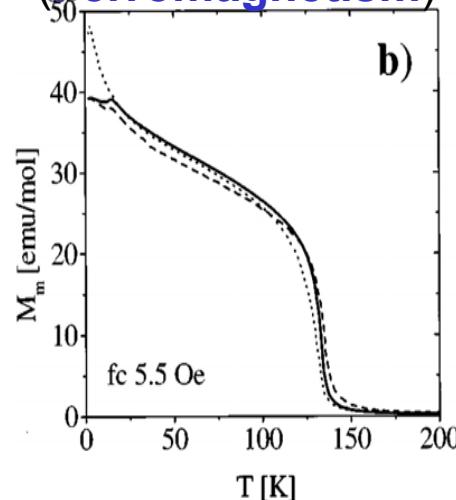
Only the combination of neutron and muon data allows the correct interpretation of the data

Example: $\text{RuSr}_2\text{GdCu}_2\text{O}_8$

Resistivity:
(Superconductivity)



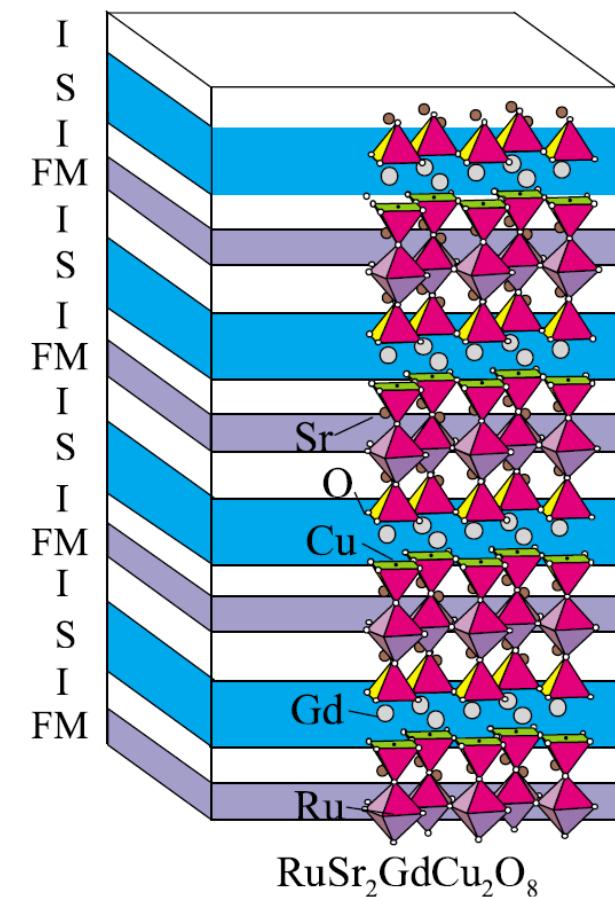
Magnetization:
(Ferromagnetism)



C. Bernhard et al., Phys. Rev. B 59 (1999) 14099

~100%
magnetic volume

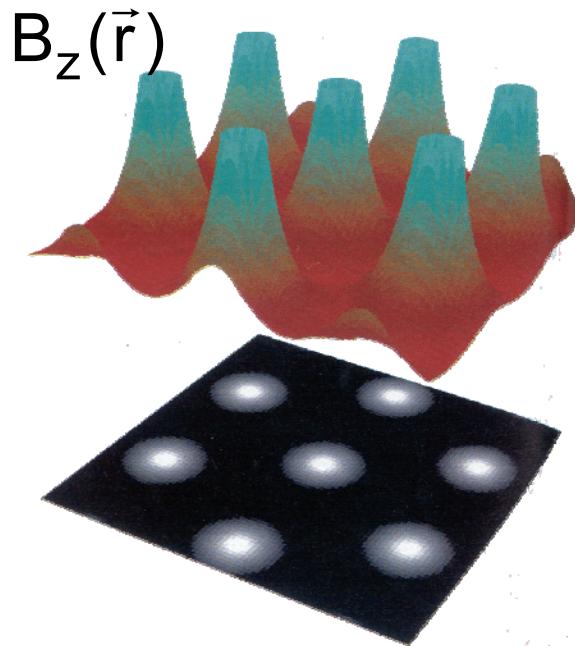
Microscopic
coexistence of
superconductivity
and magnetism



Structure:

T. Nachtrab et al., Phys. Rev. Lett. 92 (2004) 117001

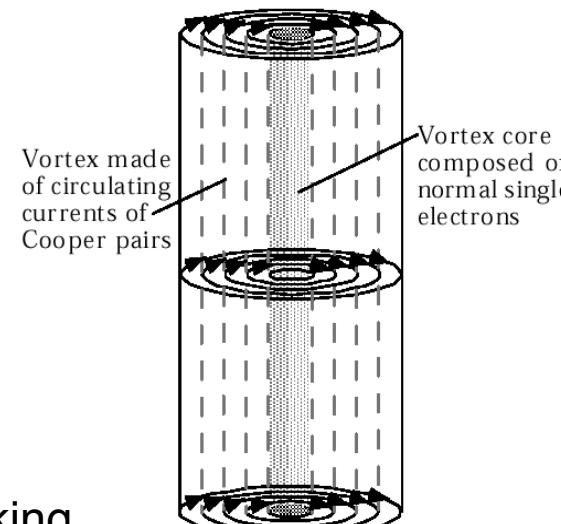
Vortex state of a type II superconductor



1 vortex:

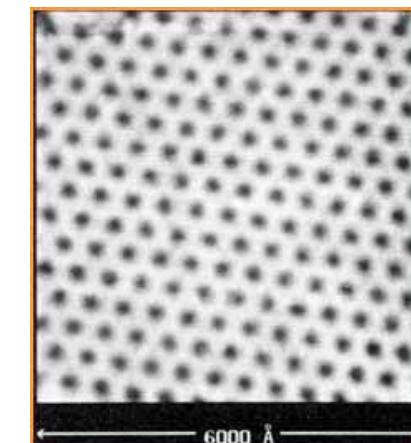
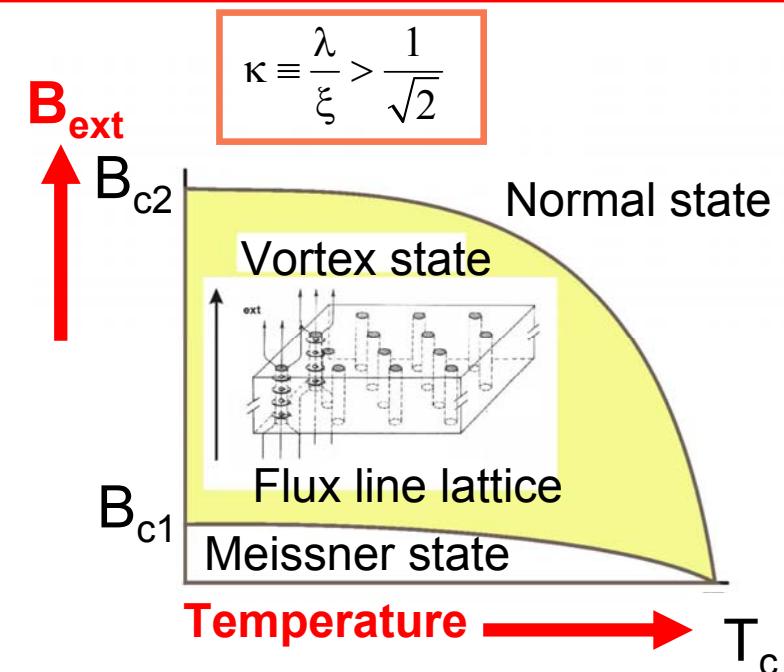
$$\Phi_0 = \frac{h}{2e}$$

Flux generated is one quantum of flux
 $\phi = \Phi_0 = h/2e$



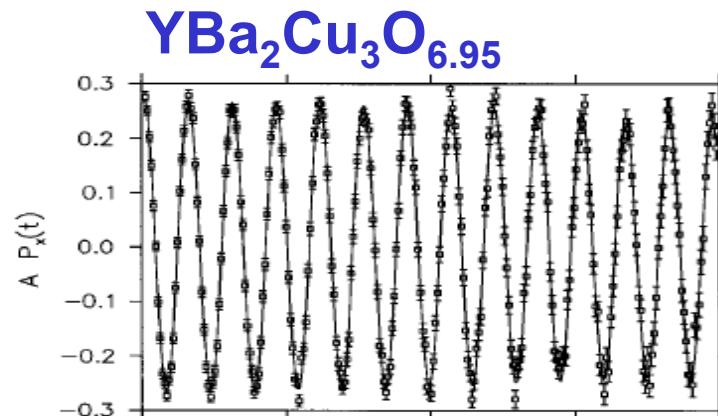
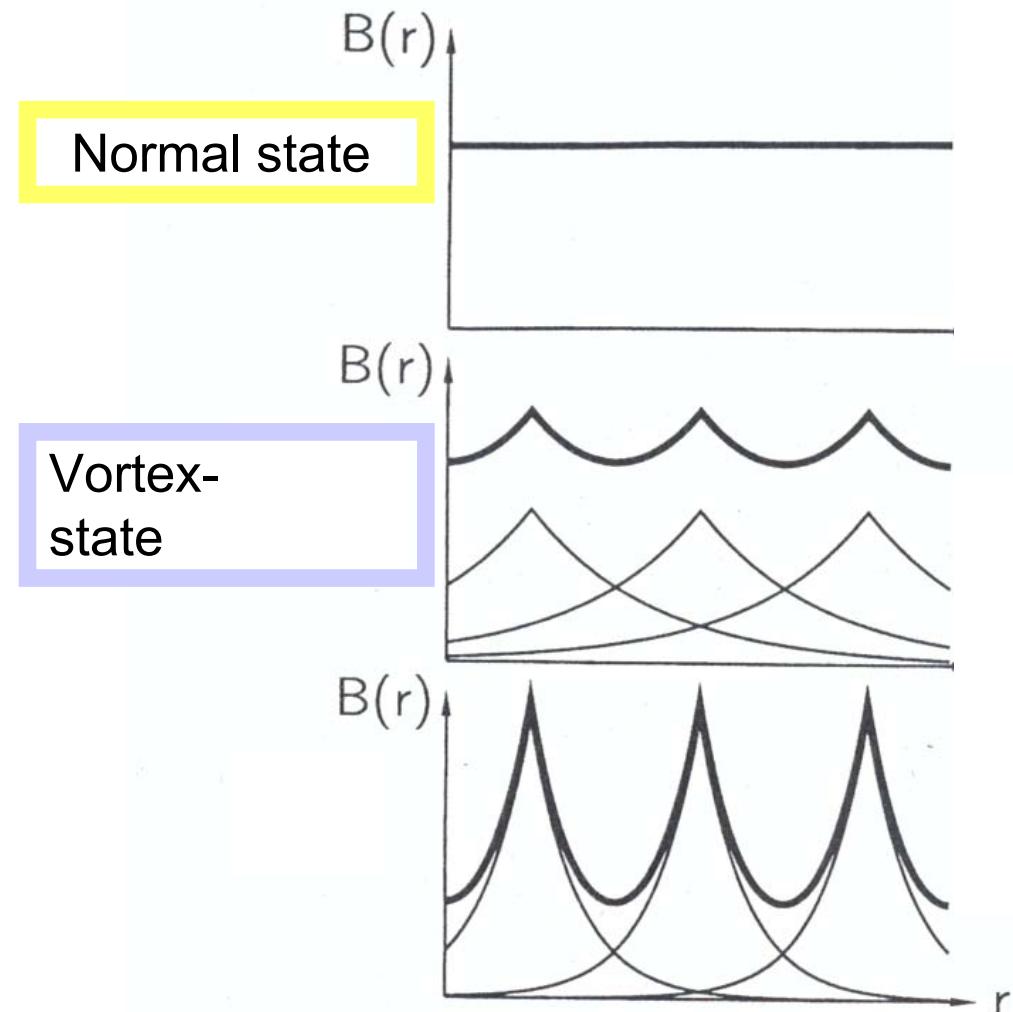
$B(r)$ can be obtained from a modified London equation taking into account the flux generated by the regular array of vortices

$$\Delta \vec{B}(\vec{r}) - \frac{\vec{B}(\vec{r})}{\lambda^2} = \frac{\Phi_0}{\lambda^2} \sum_{\vec{R}} \delta(\vec{r} - \vec{R}) \hat{z}$$

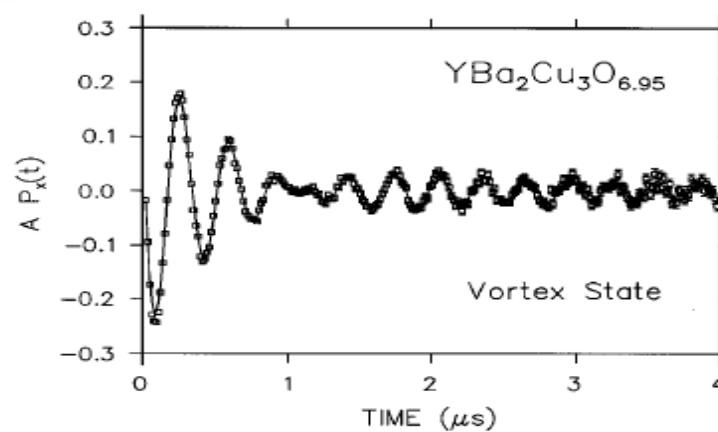


Surface image by Scanning Tunnel Microscopy
 $NbSe_2$, 1T, 1.8K
H. F. Hess et al. Phys. Rev. Lett. 62, 214 (1989)

μ SR in the vortex state



$$AP_x(t) = A \cos(\gamma_\mu Bt + \Phi)$$



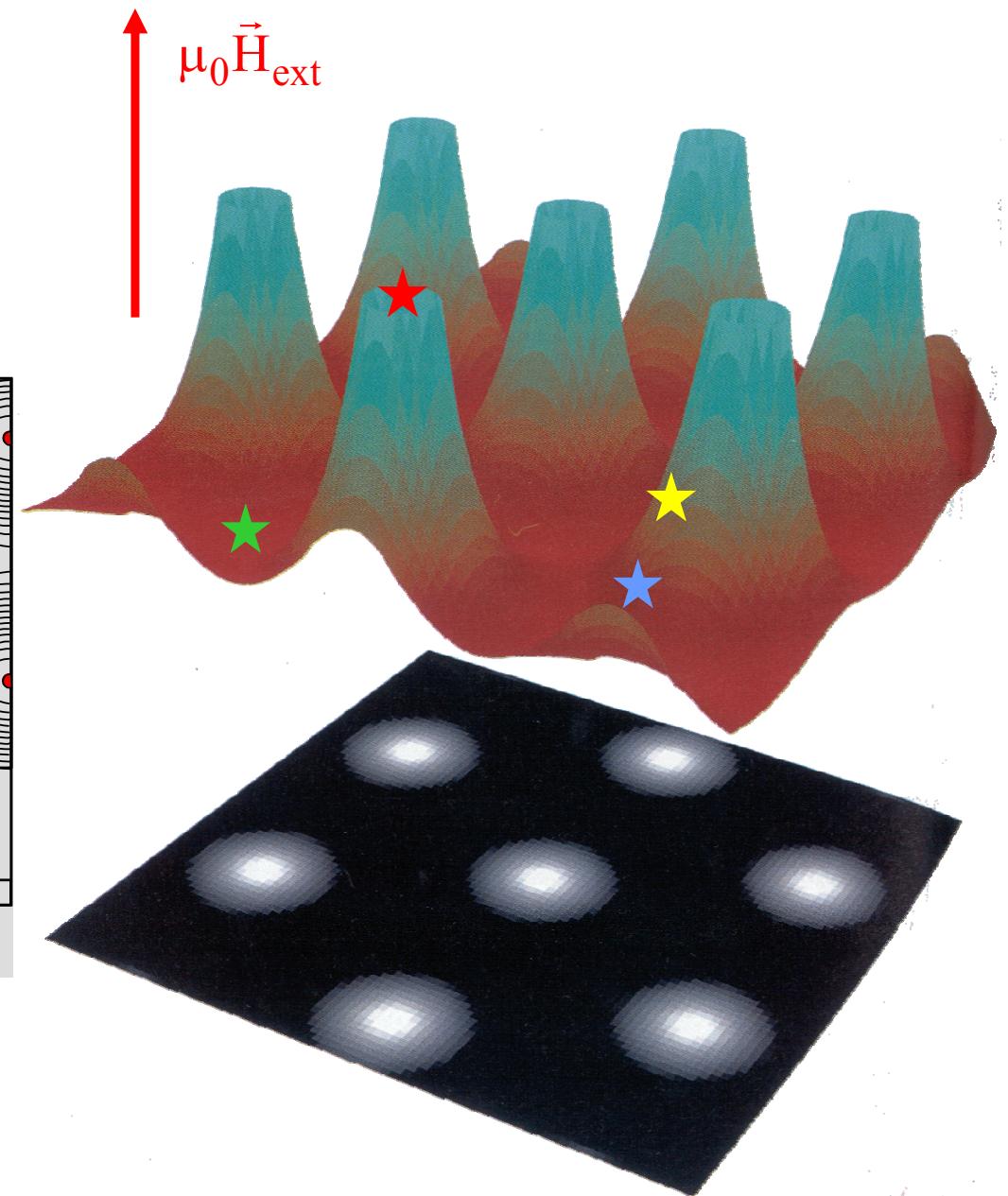
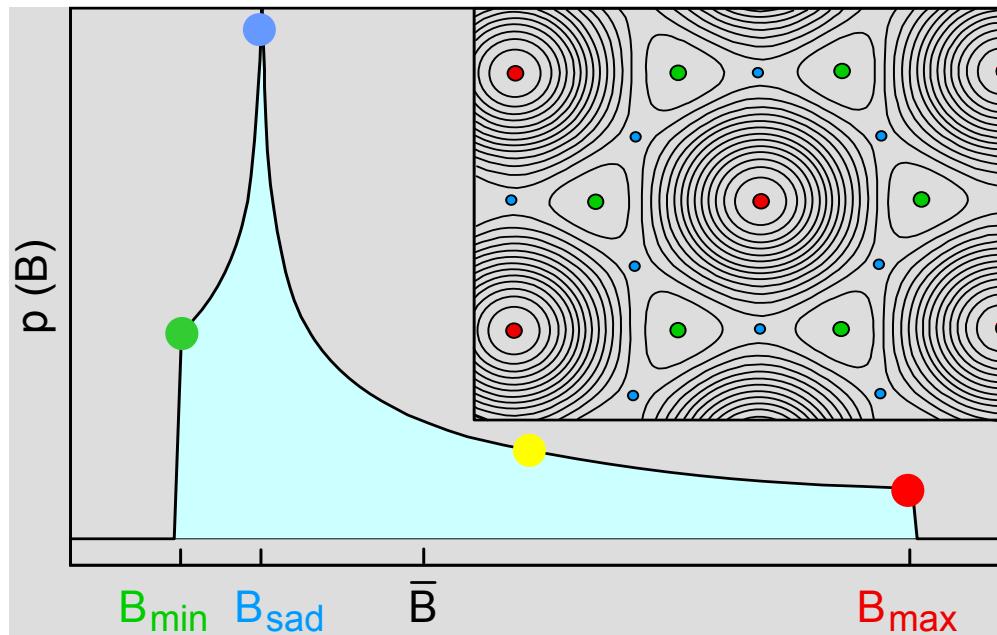
$$P_x(t) = \frac{1}{N} \sum_{i=1}^N \cos(\gamma_\mu B(\vec{r}_i) t + \phi)$$

$$P_x(t) = \int p(B_z) \cos(\gamma_\mu B_z t + \phi) dB_z$$

Field distribution vortex state

$$P_x(t) = \int p(B_z) \cos(\gamma_\mu B_z t + \phi) dB_z$$

$p(B_z)$: field distribution
(field averaged over all muon sites)

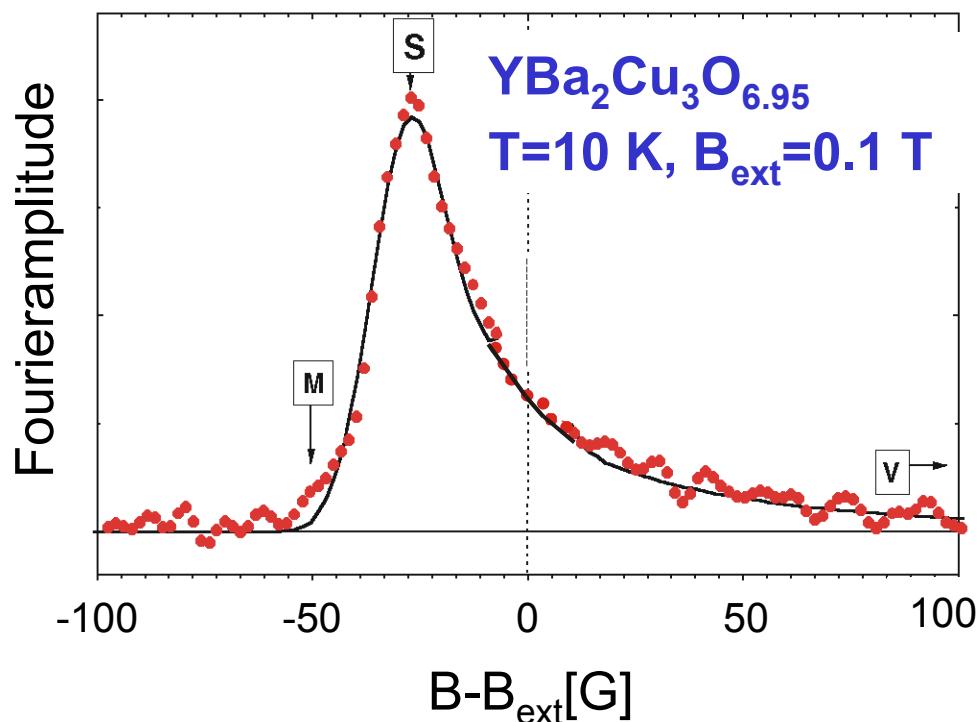


Bishop et al., Scientific American 48 (1993)

Field distribution in vortex state

$$P_x(t) = \int p(B_z) \cos(\gamma_\mu B_z t + \phi) dB_z$$

$p(B_z)$: microscopic magnetic field distribution $p(B_z) \longleftrightarrow B_z(r)$
= Fourier transform of time evolution of polarization $P(t)$



- Structure, symmetry of the Flux line lattice
- Vortex motion
- Charakteristic lengths: magnetic penetration depth λ , radius of the vortex core (coherence length)
- Classification scheme of superconductors

Spatial dependence of field and field width

$$\Delta \vec{B}(\vec{r}) - \frac{\vec{B}(\vec{r})}{\lambda^2} = \frac{\Phi_0}{\lambda^2} \sum_{\vec{R}} \delta(\vec{r} - \vec{R}) \hat{z}$$

can be explicitly solved in reciprocal space:

$$B_z(\vec{r}) = \sum_{\vec{k}} \frac{\langle B \rangle}{1 + \lambda^2 k^2} e^{i\vec{k}\vec{r}}$$

and the second moment calculated

$$\langle \Delta B_z^2 \rangle = \langle B_z^2 \rangle - \langle B_z \rangle^2$$

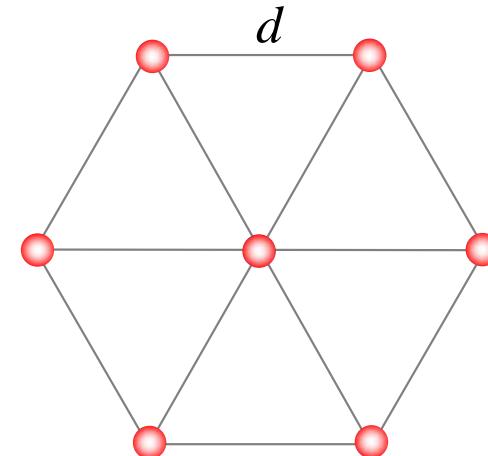
we obtain:

$$\langle \Delta B_z^2 \rangle = 0.00371 \frac{\Phi_0^2}{\lambda^4}$$

A μ SR measurement of the second moment of the field distribution allows to determine the London penetration depth λ .

$$\rightarrow \lambda(T) = \sqrt{\frac{m^*}{\mu_0 e^2 n_s(T)}}$$

n_s : supercarrier density, m^* : effective mass



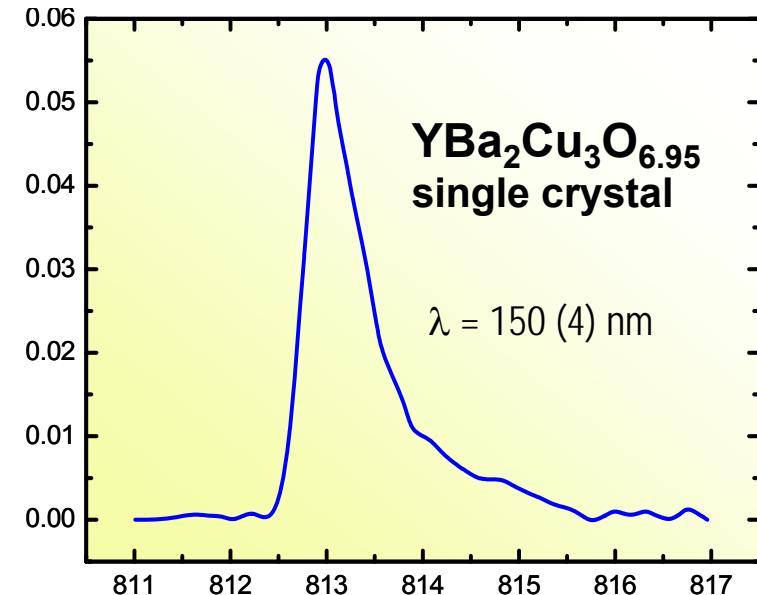
Field distribution in vortex state

Single crystals:

asymmetric field distribution.

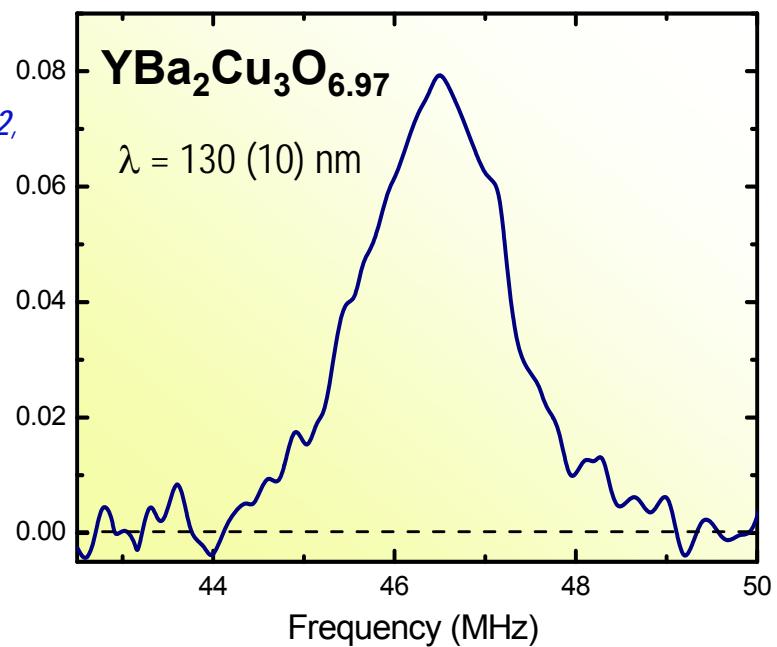
Allow to study anisotropic properties of high temperature superconductors

Sonier et al.,
PRL 83, 4156
(1999)



Polycrystals or sintered samples:
large density and disorder of pinning sites → strong smearing of the field distribution. Can be approximated by Gauss distribution

Pümpin et al.,
Phys. Rev. B 42,
8019 (1990)



Gauss field distribution and polarization

Gaussian damped precession

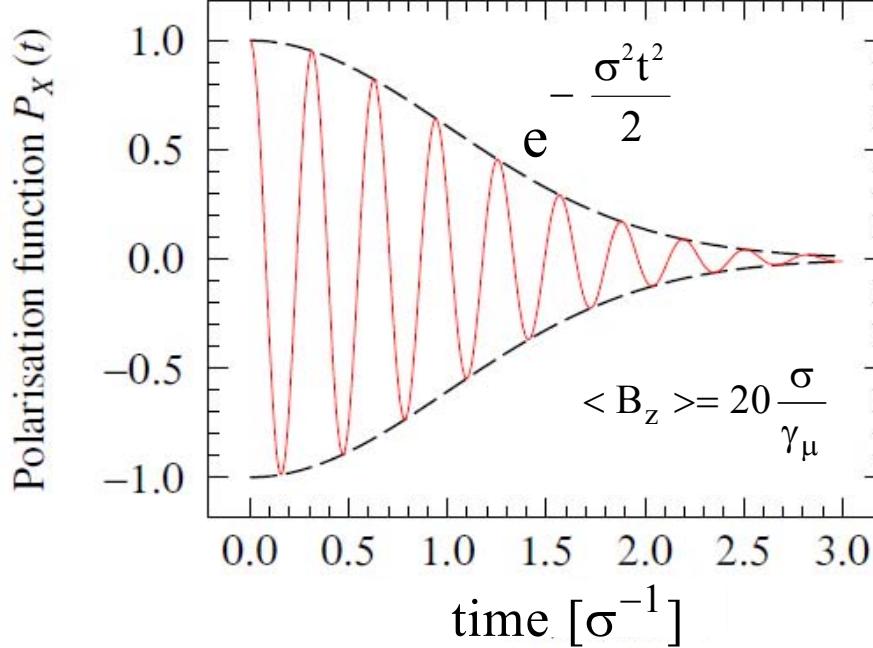
$$P(t) = e^{-\frac{\sigma^2 t^2}{2}} \cos(\gamma_\mu \langle B_z \rangle t)$$

$$\sigma^2 = \gamma_\mu^2 \langle \Delta B_z^2 \rangle$$

Relaxation rate [μs^{-1}]

$$\sigma = \gamma_\mu \Phi_0 \sqrt{0.00371} \frac{1}{\lambda^2}$$

$$\sigma [\mu\text{s}^{-1}] = 0.1074 \frac{1}{\lambda [\mu\text{m}]^2}$$

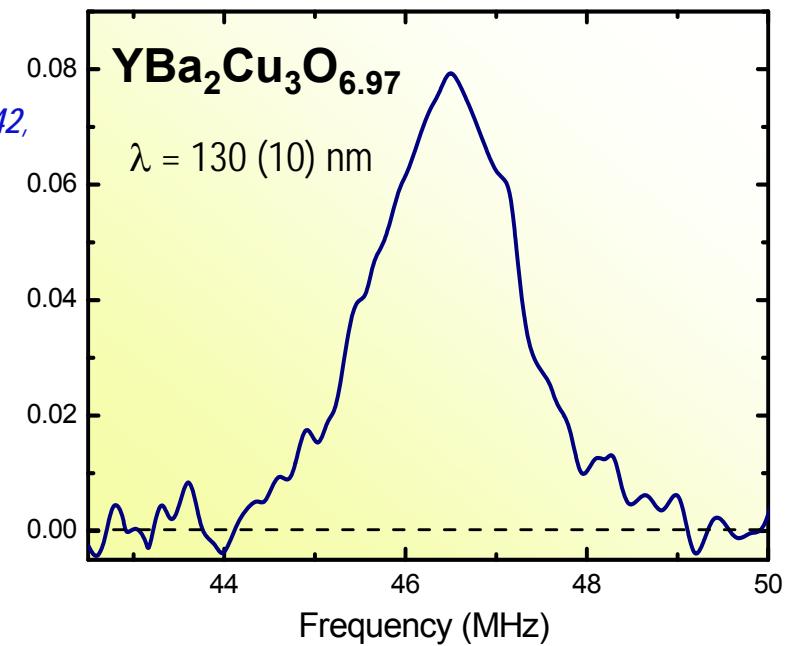


Gaussian field distribution

$$p(B_z) = \frac{\gamma_\mu}{\sqrt{2\pi}\sigma} e^{-\frac{\gamma_\mu^2 (\langle B_z \rangle - B_z)^2}{2\sigma^2}}$$

$$\frac{\sigma^2}{\gamma_\mu^2} = \langle \Delta B_z^2 \rangle$$

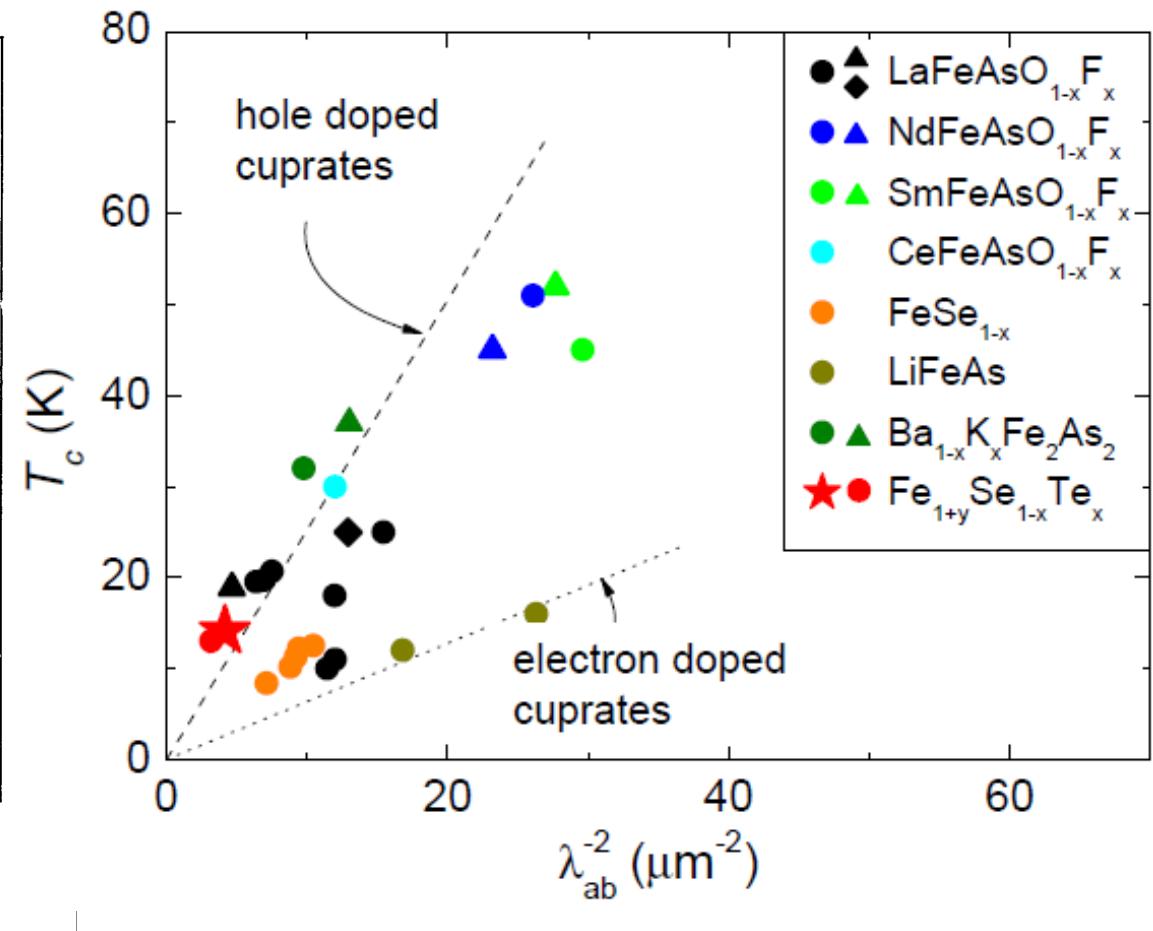
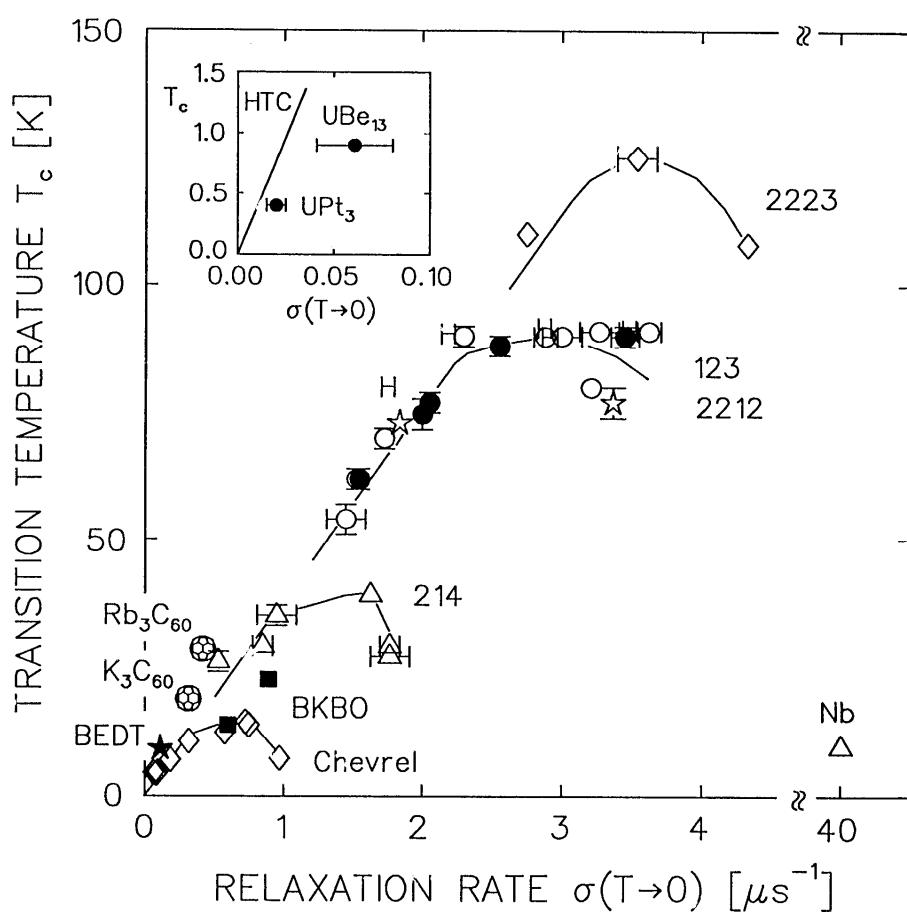
Pümpin et al.,
Phys. Rev. B 42,
8019 (1990)



Classification of superconductors

Y.Uemura et al., Phys. Rev. Lett. 66, 2665 (1991)

$$T_c \text{ versus } \sigma \propto \frac{1}{\lambda^2} \propto \frac{n_s}{m^*}, \text{ Uemura plot}$$



T-dependence of sc carrier density and sc gap

From μ SR:

$$\sigma_\mu = \gamma_\mu \sqrt{\langle \Delta B^2 \rangle} \propto \frac{1}{\lambda^2}$$

$$\lambda = \sqrt{\frac{m}{\mu_0 e^2 n_s}}$$

$$\Rightarrow \sigma_\mu \propto \frac{\mu_0 e^2}{m} n_s$$

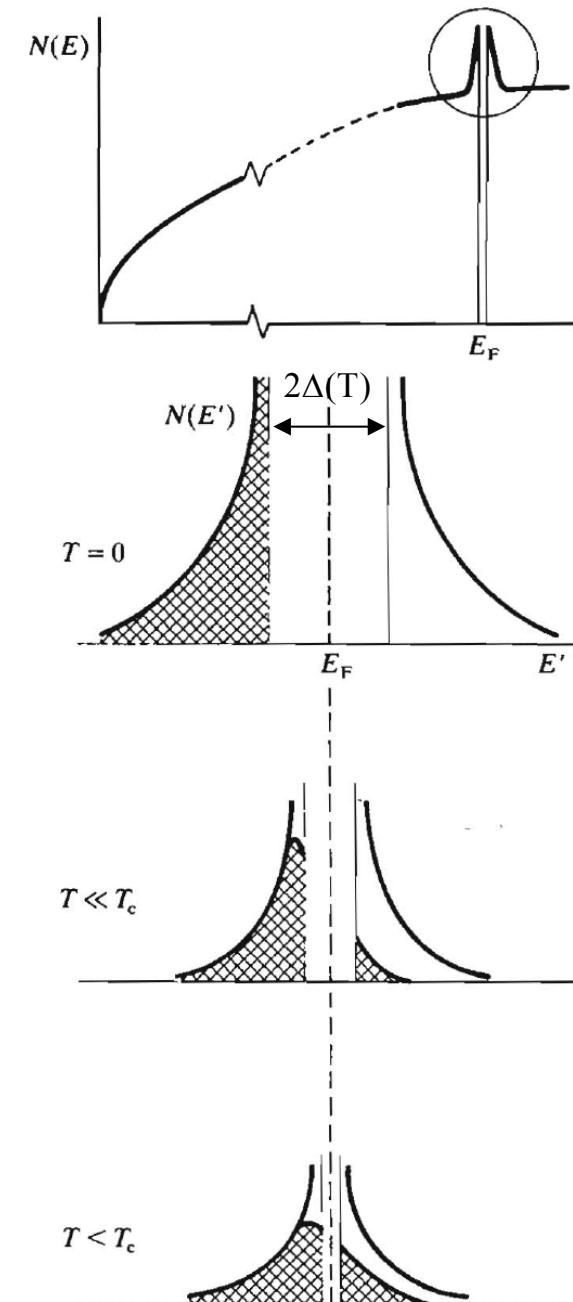
indications on the SC gap

By taking into account the thermal population of the quasiparticles excitations of the Cooper pairs (Bogoliubov quasiparticles):

$$n_s(T) = n_s(0) \left(1 - \frac{2}{k_B T} \int_0^\infty f(\epsilon, T) [1 - f(\epsilon, T)] d\epsilon \right)$$

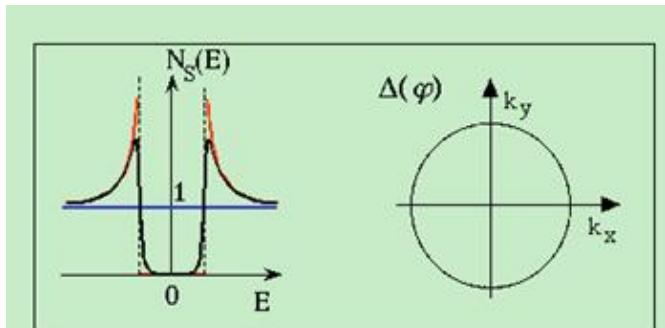
with:

$$f(\epsilon, T) = \left(1 + \exp \left[\sqrt{\epsilon^2 + \Delta(T)^2} / k_B T \right] \right)^{-1}$$



T-dependence of sc carrier density and sc gap

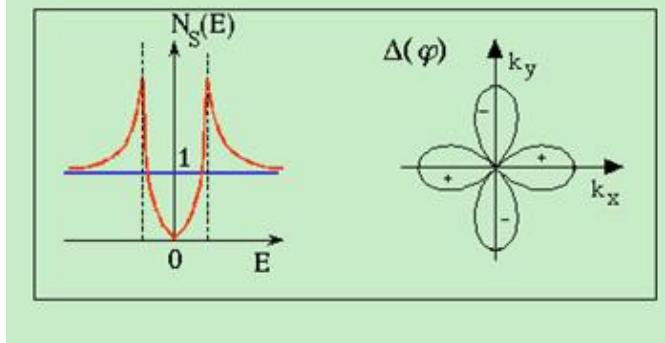
Low temperature dependence of magnetic penetration depth reflects symmetry of superconducting gap function



s – wave gap

$$\Delta(T,\varphi)=\Delta(T)$$

$$\lambda(T) = \lambda(0) \left(1 + \sqrt{\frac{\pi\Delta(0)}{2k_B T}} \exp[-\Delta(0)/k_B T] \right)$$



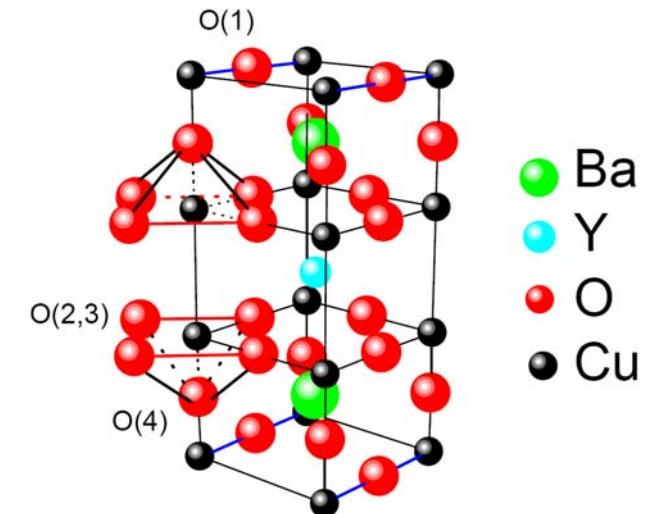
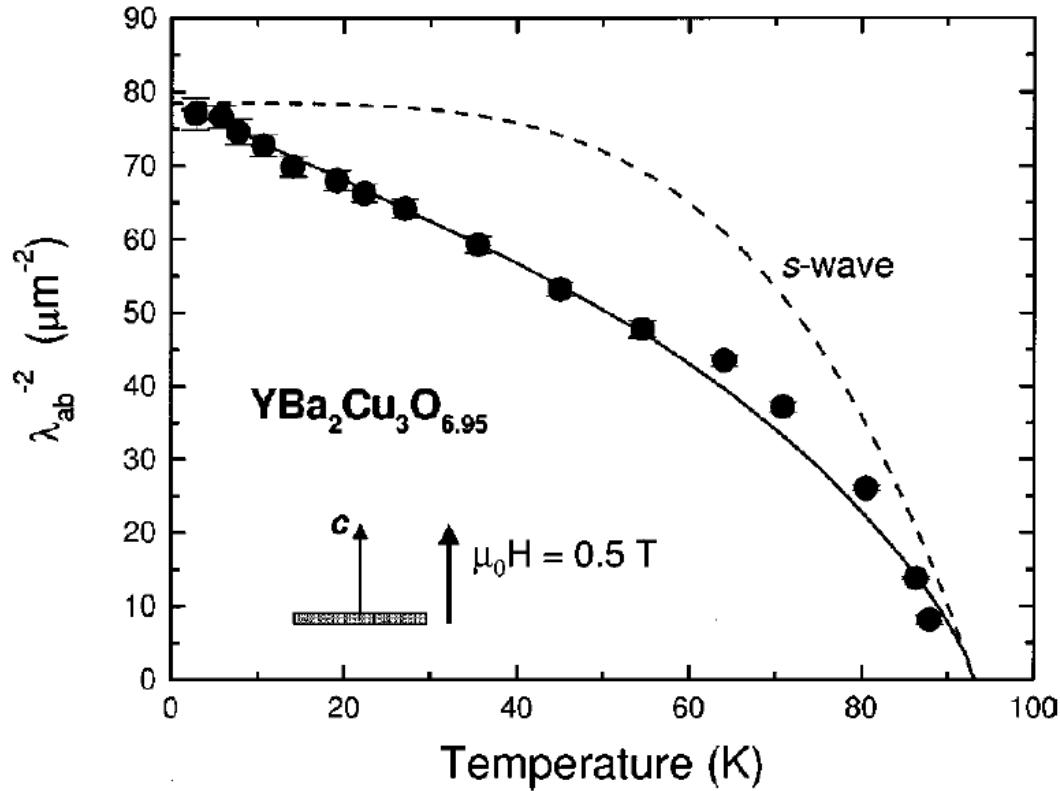
d – wave gap

$$\Delta(T,\varphi)=\Delta(T)\cos(2\varphi)$$

$$\tan \varphi = \frac{k_y}{k_x}$$

$$\lambda(T) = \lambda(0) \left(1 + \frac{\ln 2}{\Delta(0)} T \right)$$

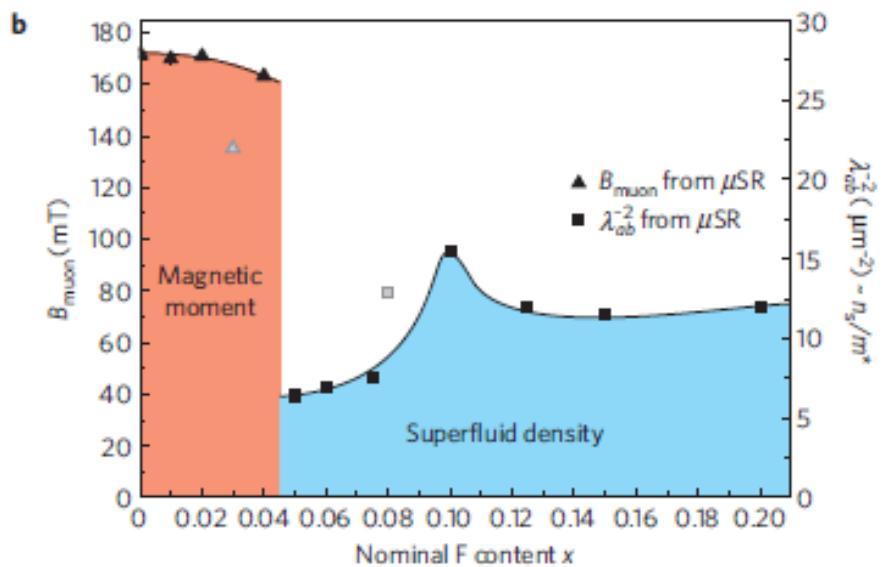
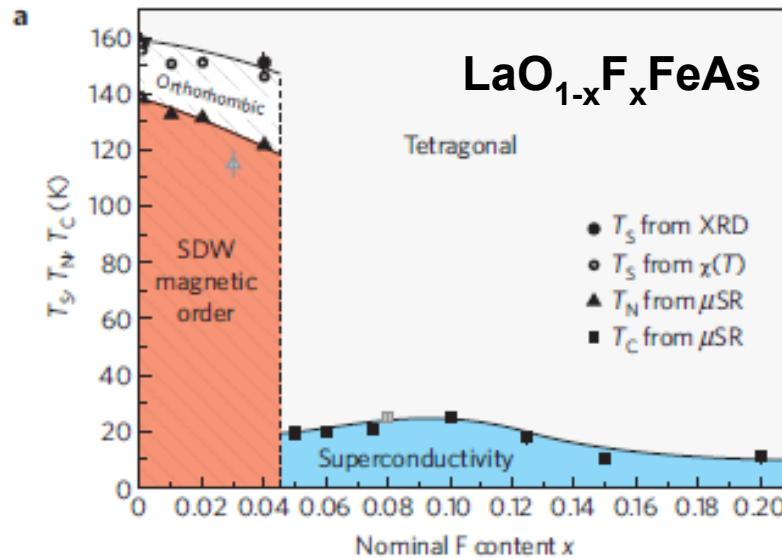
T-dependence of sc carrier density and sc gap



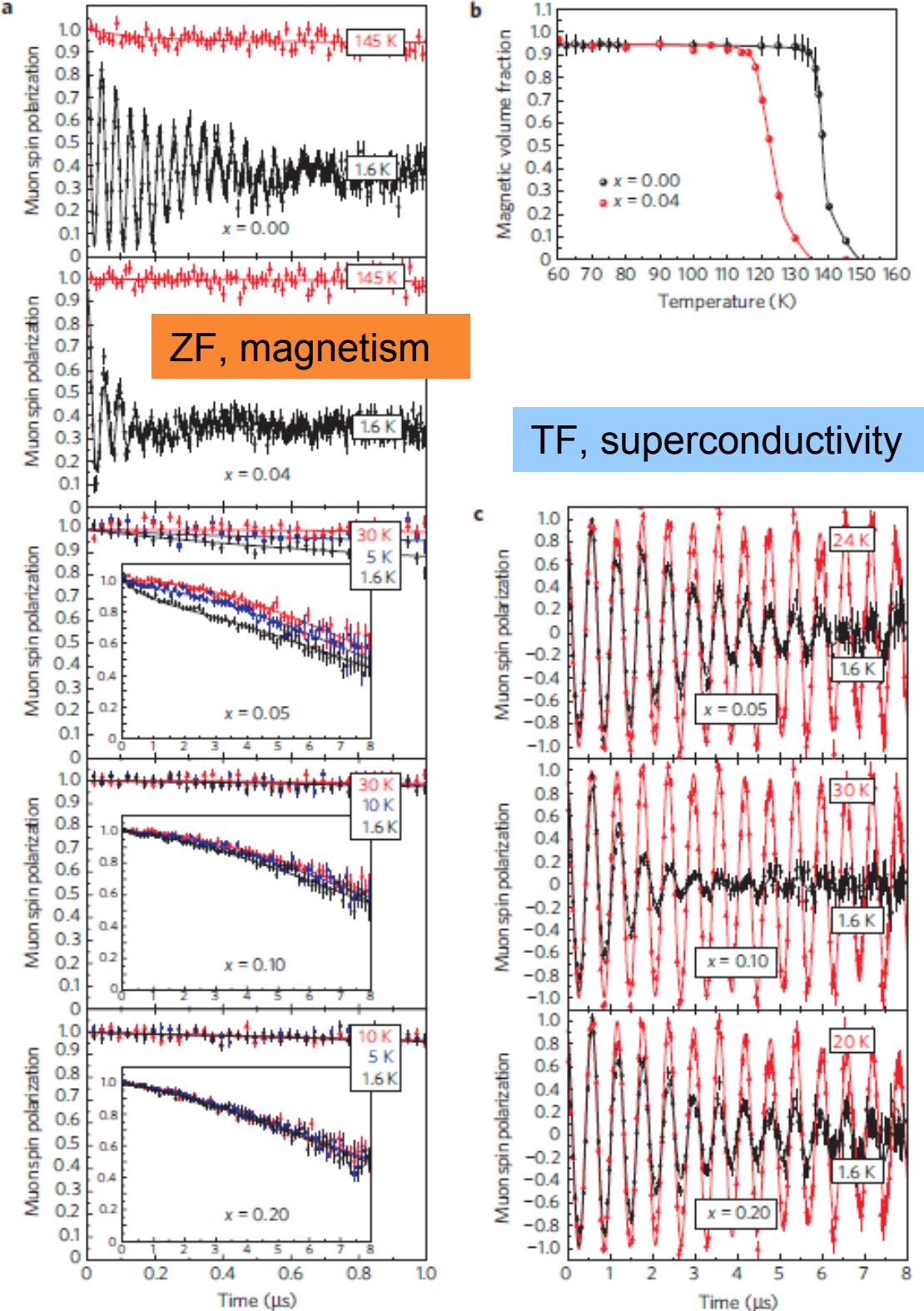
μ SR measurement: *J. Sonier et al., Phys. Rev. Lett., 72, 744 (1994)*

microwave measurement: *W.N. Hardy et al., Phys. Rev. Lett 70, 3999 (1993)*

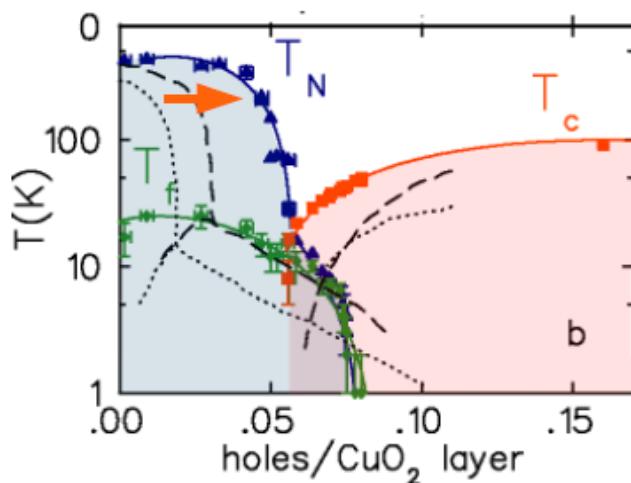
Phase diagram



H. Luetkens et al., Nature Materials 8, 305 - 309 (2009)



Coexistence of magnetic and sc order: $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$

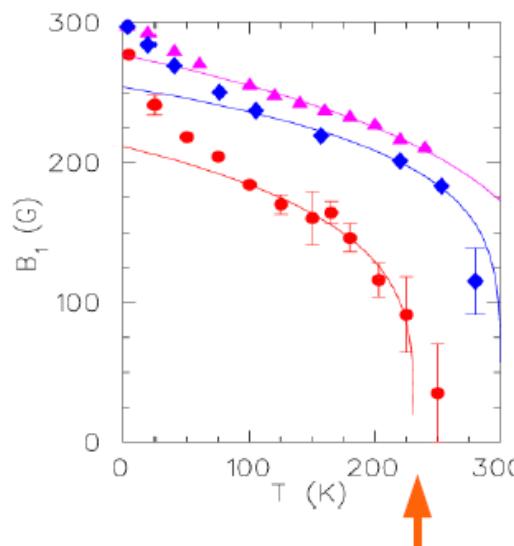


Magnetism from ZF measurements:

$$A_z(t) = a_L G_z(t) + a_T G_x(t) \cos(\gamma_\mu |\vec{B}_1| t)$$

$$a_L + a_T = a_{ZF}$$

\vec{B}_1 : local field



Magnetic volume fraction:

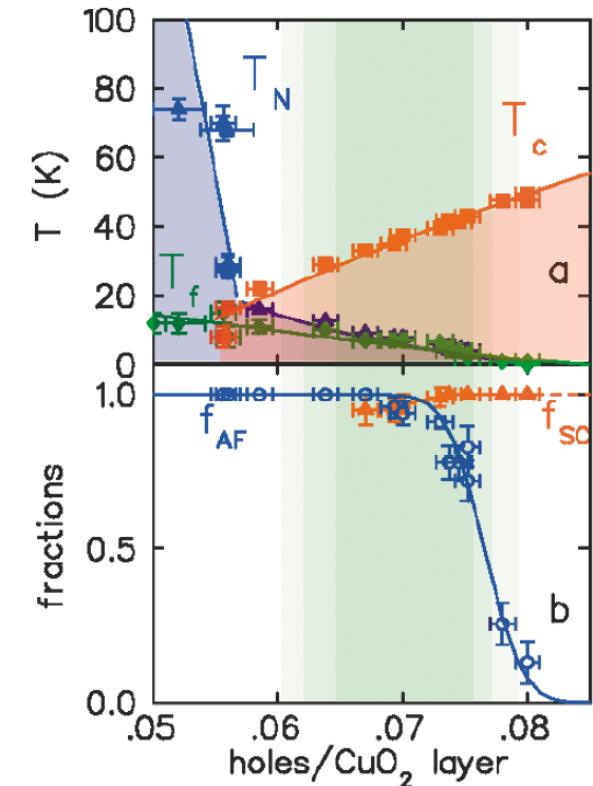
$$f_{AF} = \frac{3}{2} \frac{a_T}{a_{ZF}} = \frac{3}{2} \left(1 - \frac{a_L}{a_{ZF}}\right)$$

for a homogeneous magnetic sample:

$$\frac{a_L}{a_{ZF}} = \frac{1}{3} \quad \text{and} \quad \frac{a_T}{a_{ZF}} = \frac{2}{3}$$

if only part of the sample is magnetic

$$\frac{a_L}{a_{ZF}} > \frac{1}{3} \quad \text{and} \quad \frac{a_T}{a_{ZF}} < \frac{2}{3}$$

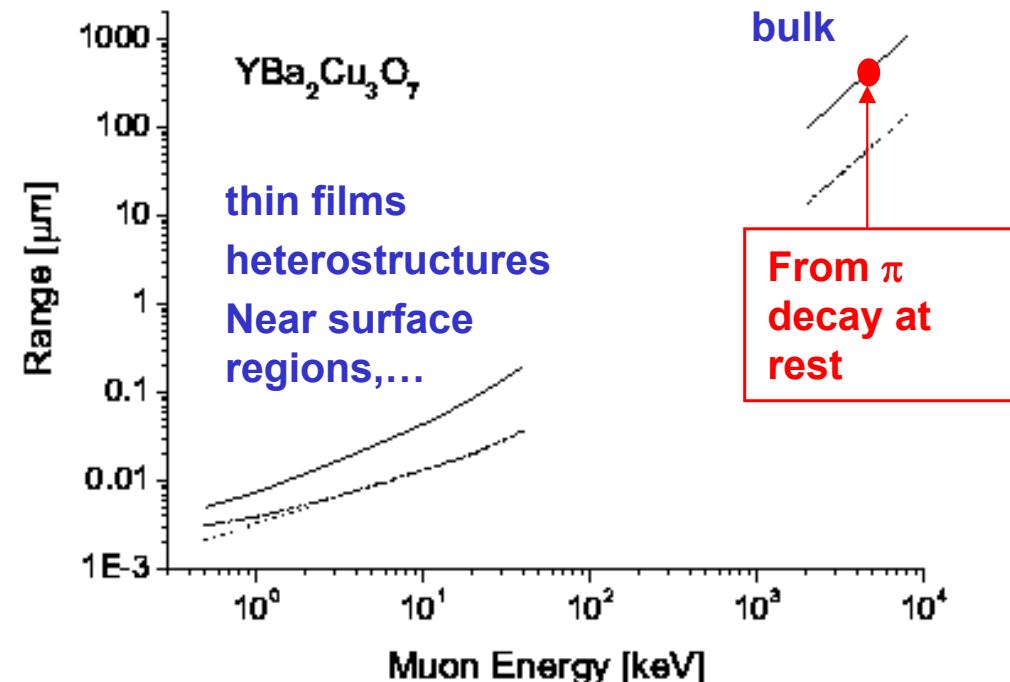
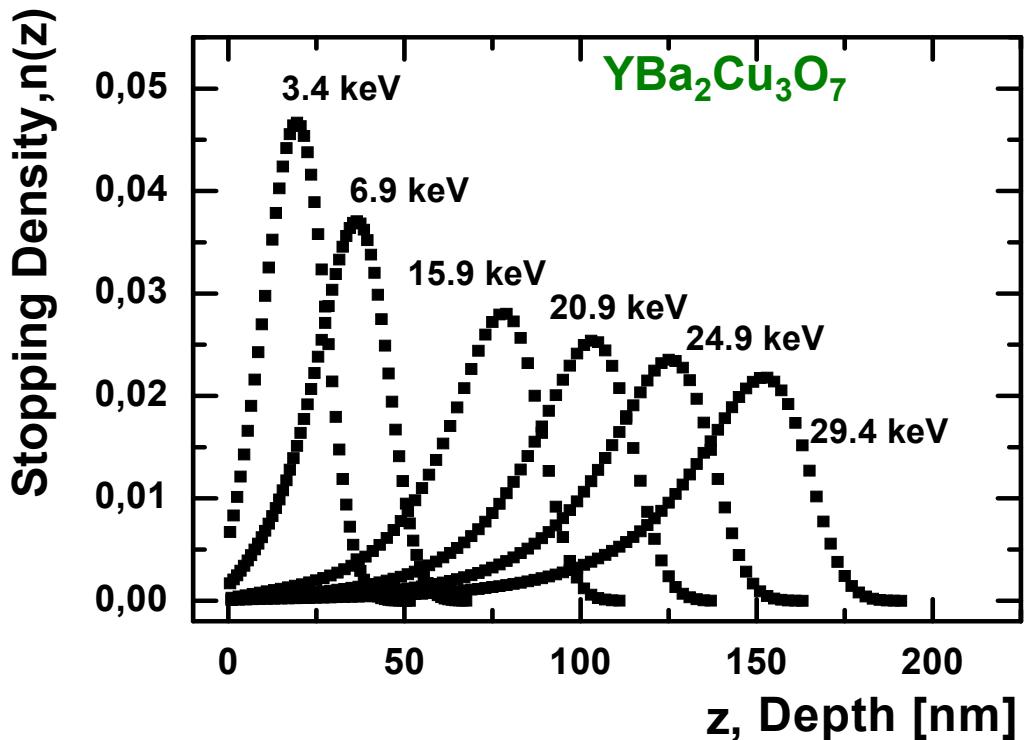


Superconductivity (vortex state) from TF

$$A_x(t) = a_{TF} e^{-\frac{(\sigma_\mu^2 + \sigma_n^2)t^2}{2}} \cos(\gamma_\mu B_\mu t)$$

$$B_\mu = \mu_0 H(1 + \chi) \quad \text{and} \quad \chi < 1$$

Implantation profiles and ranges of muons



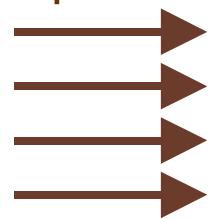
- For thin films studies we need muons with energies in the region of keV rather than MeV
- Tunable energy ($E_\mu < 30$ keV) allows depth-dependent μ SR studies ($\sim 1 - 200$ nm)
- Low energy muons are a new magnetic/spin probe for thin films, multilayers, near surface regions, buried layers,..

Stopping profiles calculated with the Monte Carlo code Trim.SP *W. Eckstein, MPI Garching*

Experimentally tested: *E. Morenzoni, H. Glückler, T. Prokscha, R. Khasanov, H. Luetkens, M. Birke, E. M. Forgan, Ch. Niedermayer, M. Pleines, NIM B192, 254 (2002).*

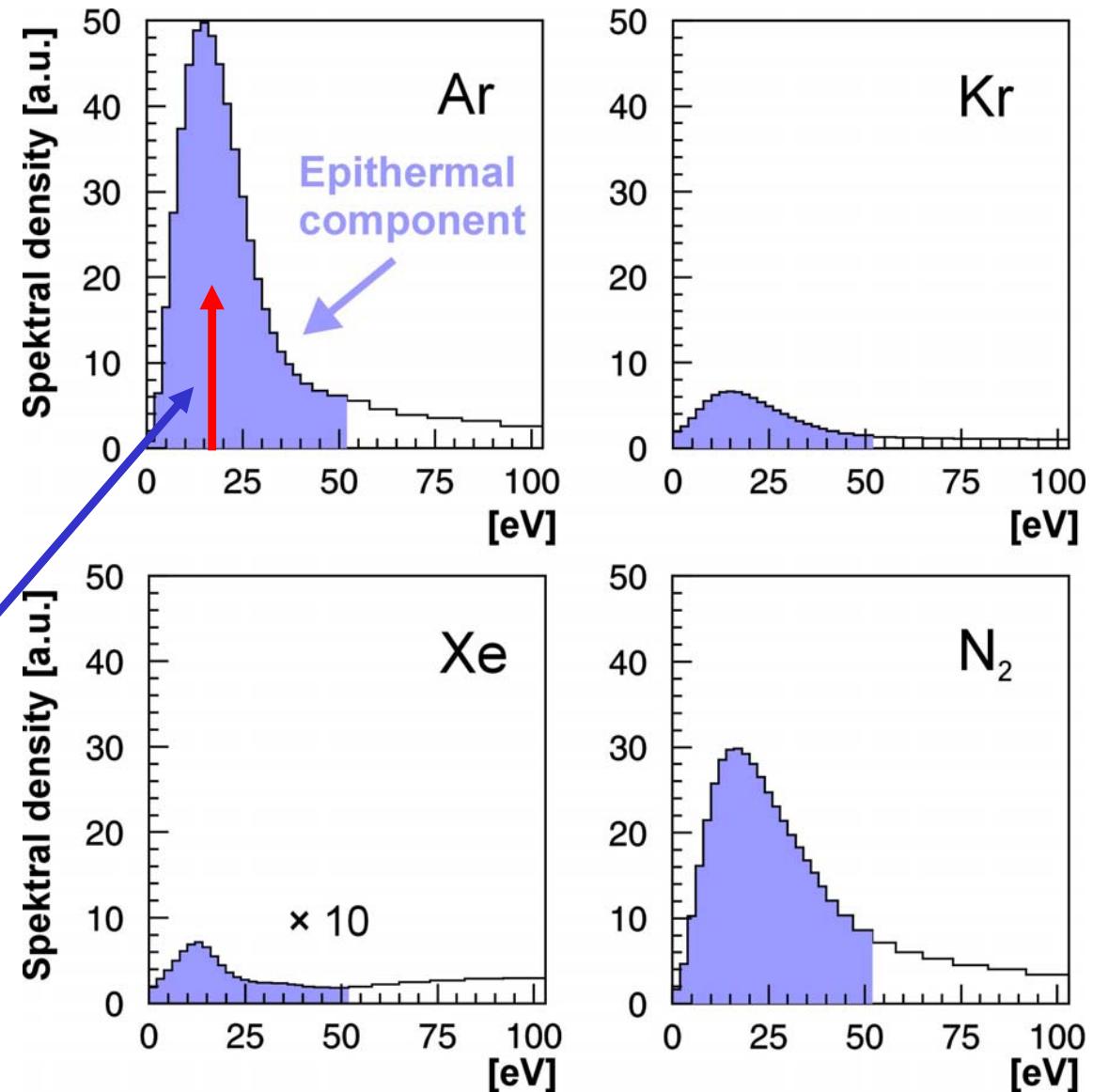
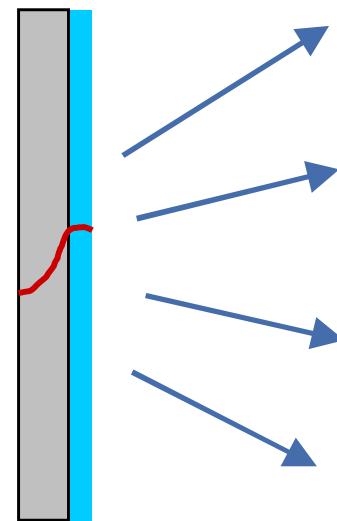
Generation of polarized epithermal muons by moderation

„Surface“
Muons
 ~ 4 MeV
 $\sim 100\%$ polarized



$\sim 100 \mu\text{m}$ Ag
6 K
 $\sim 500 \text{ nm}$
**s-Ne, Ar,
s-N₂**

**Our source of low energy
muons ($E \sim 15$ eV)**

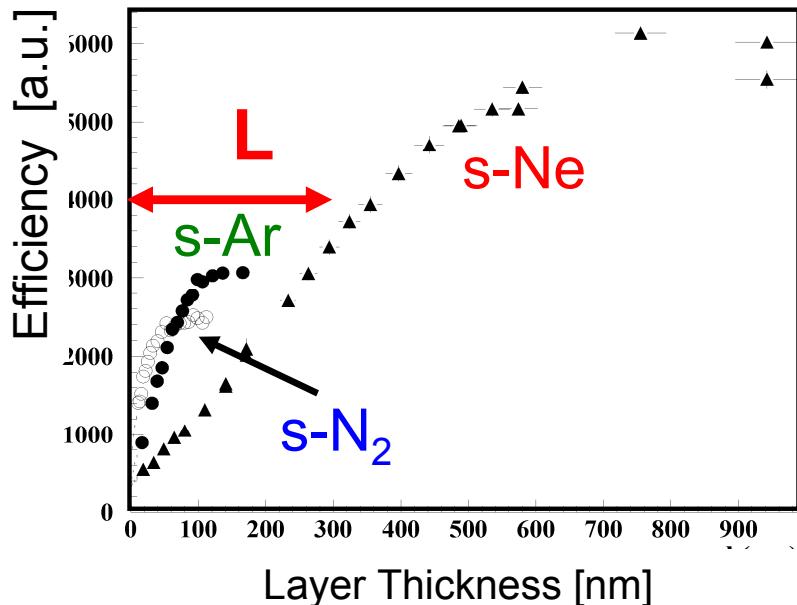


E. Morenzoni et al. J. Appl. Phys. **81**, 3340 (1997).

T. Prokscha et al. Appl. Surf. Sci. (2001)

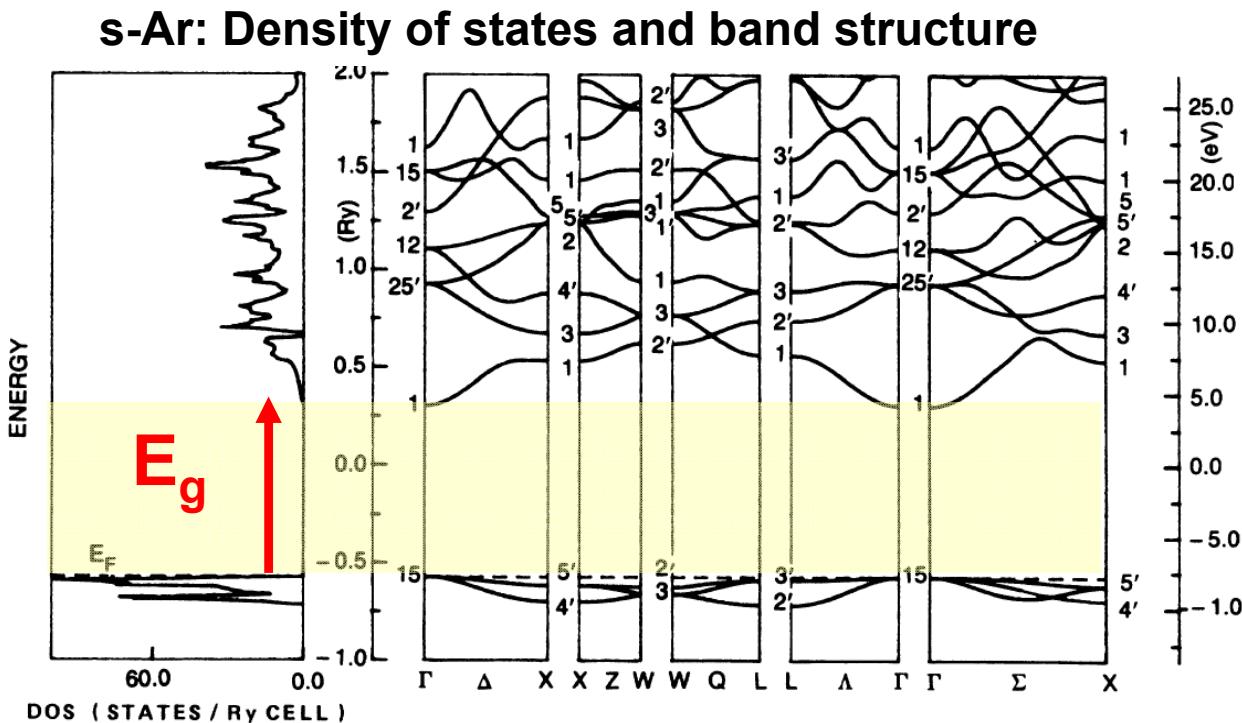
D. Harshmann et al., Phys. Rev. B36, 8850 (1987)

Characteristics of epithermal muons



Moderation mechanism:

- suppression of electronic energy loss for $E_\mu \approx E_g$ (wide band gap insulator)
- escape before thermalization
- large escape depth L (50-250 nm)



Moderation efficiency:

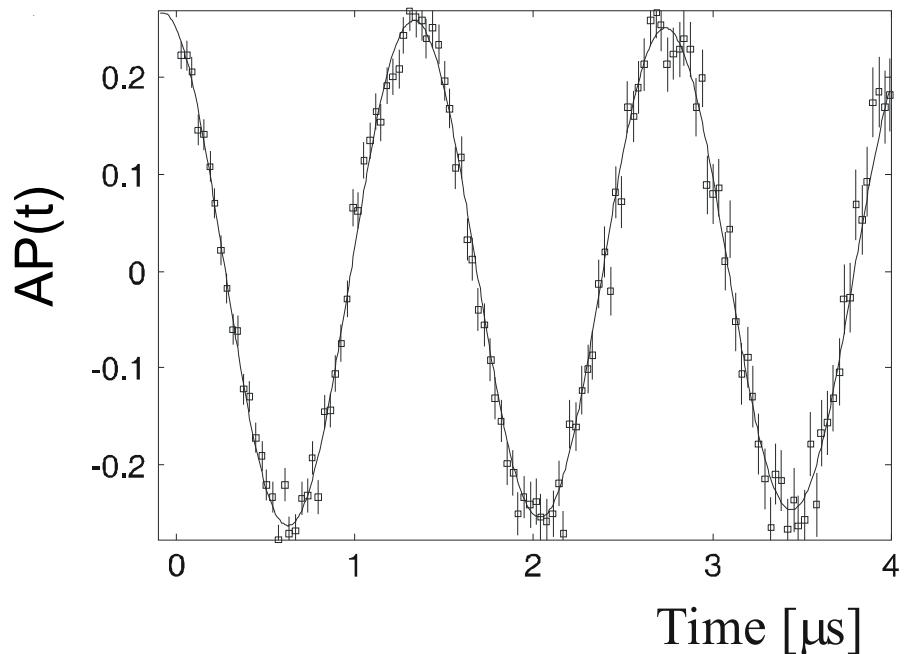
$$\varepsilon_{\mu^+} \equiv \frac{N_{\text{epith}}}{N_{4\text{MeV}}} \cong \frac{(1 - F_{\text{Mu}})L}{\Delta R} \simeq 10^{-4} - 10^{-5}$$

ΔR : Range width of surface muons $\approx 100 \mu\text{m}$

Characteristics of epithermal muons

Polarization of epithermal muons is a necessary condition for their use in μ SR

Larmor precession of epithermal muons
in an external field.



From the amplitude we conclude:

No polarization loss during moderation

(very fast slowing down time: ~ 10 ps, no depolarizing mechanism that fast)

$$\rightarrow P(0) \approx 1$$

E. Morenzoni, F. Kottmann, D. Maden, B. Matthias,
M. Meyberg, Th. Prokscha, Th. Wutzke,
U. Zimmermann, Phys.Rev.Lett. 72, 2793 (1994).

Low energy μ^+ beam and set-up for LE- μ SR

Polarized Low Energy Muon

Beam

Energy: 0.5-30 keV

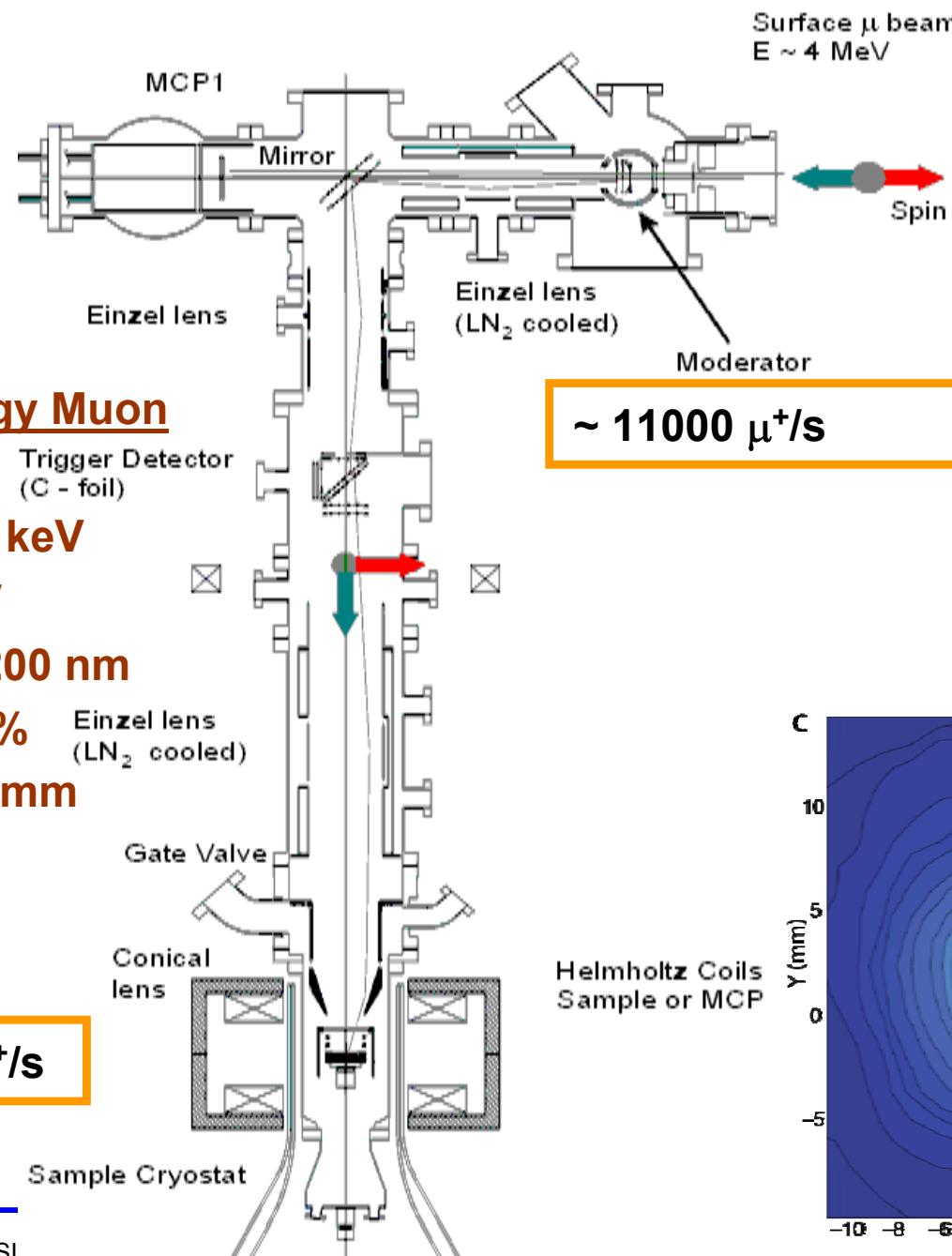
ΔE : 400 eV

Depth: ~ 1 – 200 nm

Polarization ~ 100 %

Beam Spot: 10-20 mm

$\sim 4500 \mu^+/\text{s}$

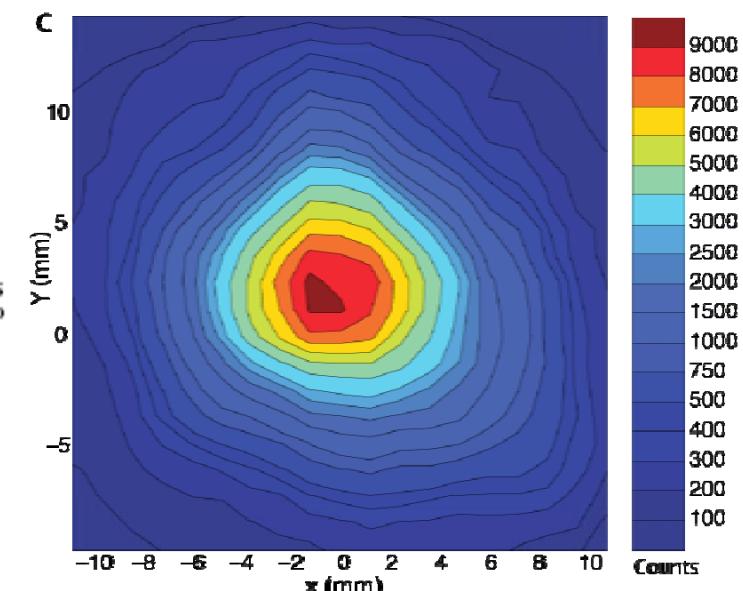


$\sim 11000 \mu^+/\text{s}$

$\sim 1.9 \cdot 10^8 \mu^+/\text{s}$

from new μ E4 beam line

- UHV system ($\sim 10^{-10} \text{ mbar}$)
- Electrostatic transport, focussing and energy selection.
- All transport elements LN₂ cooled



Thin film in the Meissner State

- $B_{\text{ext}} < B_{c1}$ || surface, $T < T_c \rightarrow B=0$ in the bulk, but not at the surface
- If $\lambda \gg \xi$ electrodynamic response described by London equations:

$$1) \quad \frac{d\vec{j}}{dt} = -\frac{1}{\mu_0 \lambda_L^2} \vec{E}$$

$$2) \quad \text{rot} \vec{j} = -\frac{1}{\mu_0 \lambda_L^2} \vec{B}$$

$$(\vec{j} = -\frac{1}{\mu_0 \lambda_L^2} \vec{A})$$

From 2), $\text{rot} \vec{B} = \mu_0 \vec{j}$ and $\text{rot}(\text{rot} \vec{B}) = \text{grad div} \vec{B} - \Delta \vec{B}$ it follows

$$\Delta \vec{B} = \frac{1}{\lambda_L^2} \vec{B}$$

which in the thin film geometry $\vec{B}_{\text{ext}} \parallel \hat{x}$ gives

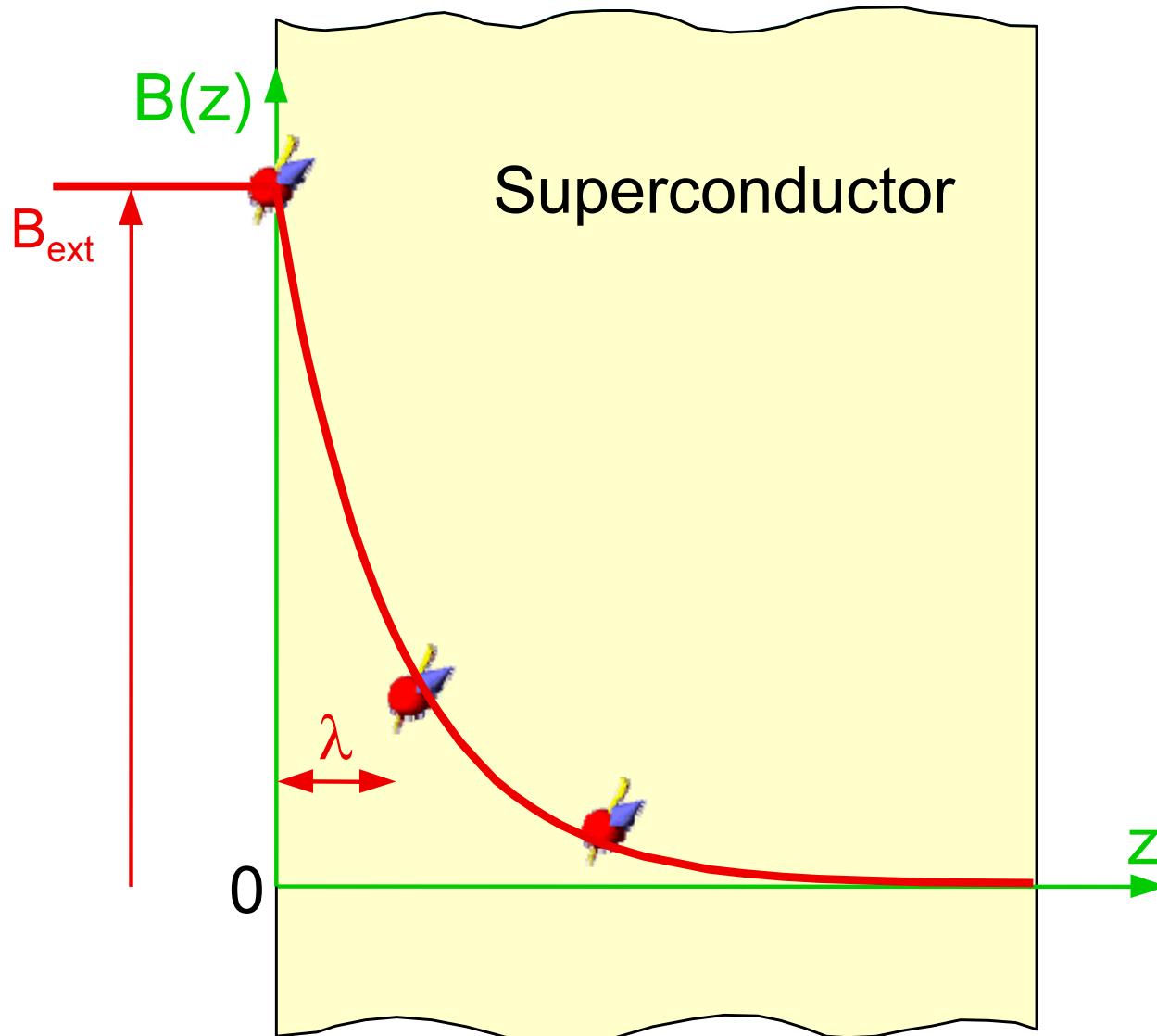
$$B(z) = B_{\text{ext}} e^{-\frac{z}{\lambda_L}} \quad \rightarrow \lambda(T) = \sqrt{\frac{m^*}{\mu_0 e^2 n_s(T)}} \quad (\text{clean limit } \ell \gg \xi_0)$$

λ_L magnetic penetration depth (London)

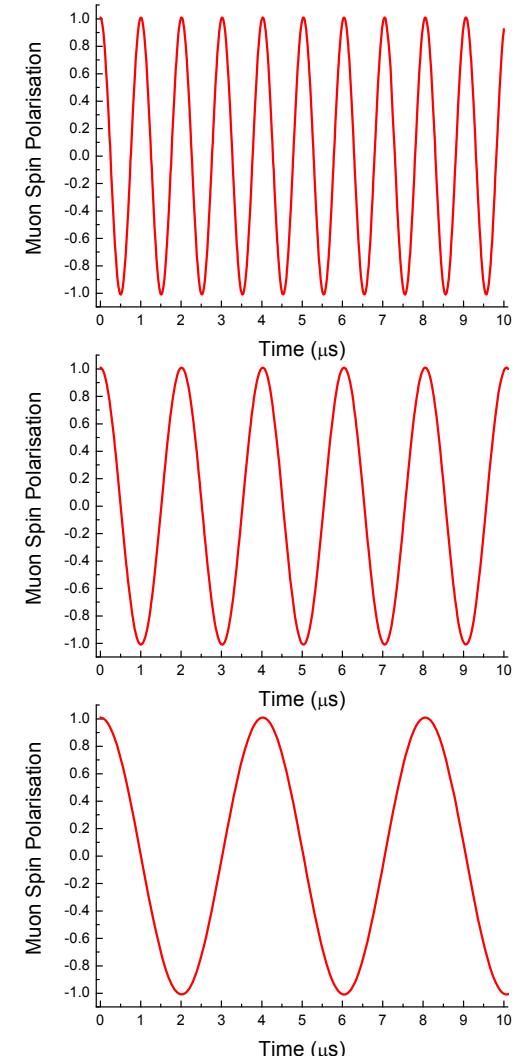
m^* , n_s effective mass and density of superconducting carriers

*F. and H. London,
Proc. Roy. Soc. A149, 71 (1935)*

Depth dependent μ SR measurements



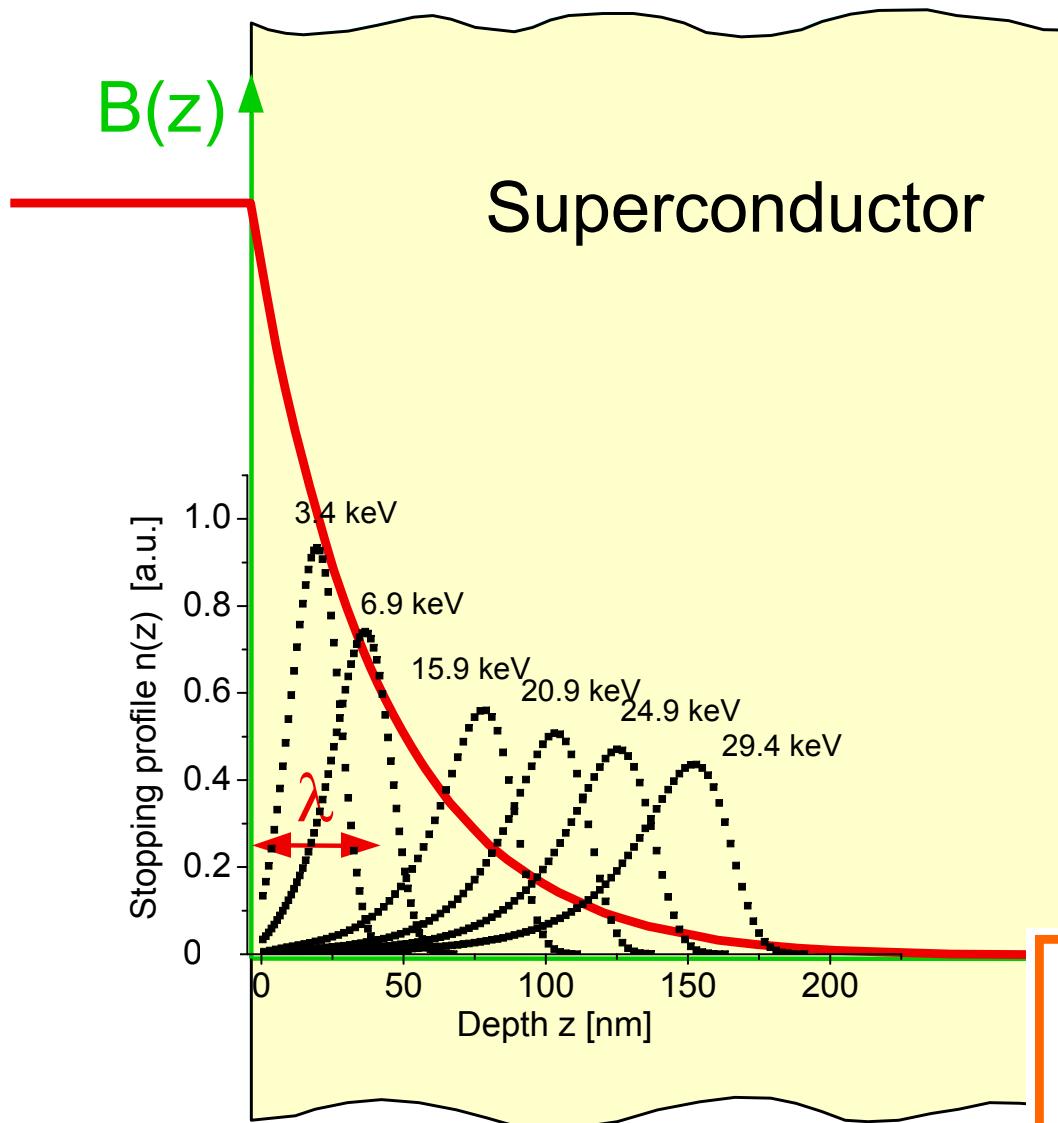
- Magnetic field profile $B(z)$ over nm scale
- Characteristic lengths of the sc λ, ξ



$$\omega_\mu(z) = \gamma_\mu B_{\text{loc}}(z)$$

$\langle B \rangle$ vs $\langle z \rangle \Rightarrow B(z)$

More precise: use known implantation profiles



$n(z, E)$: muon implantation profile for a particular muon energy E

μ SR experiment \Rightarrow magnetic field probability distribution $p(B, E)$ sensed by the muons



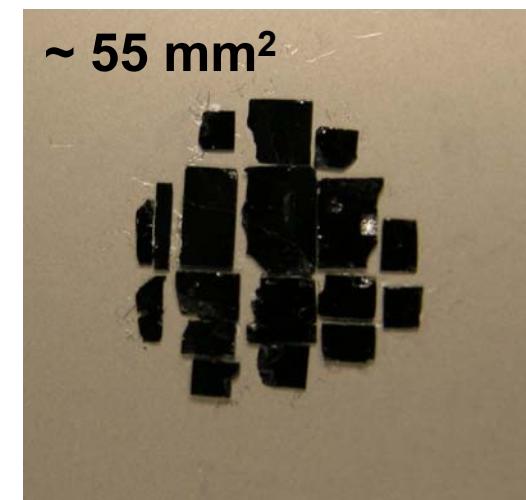
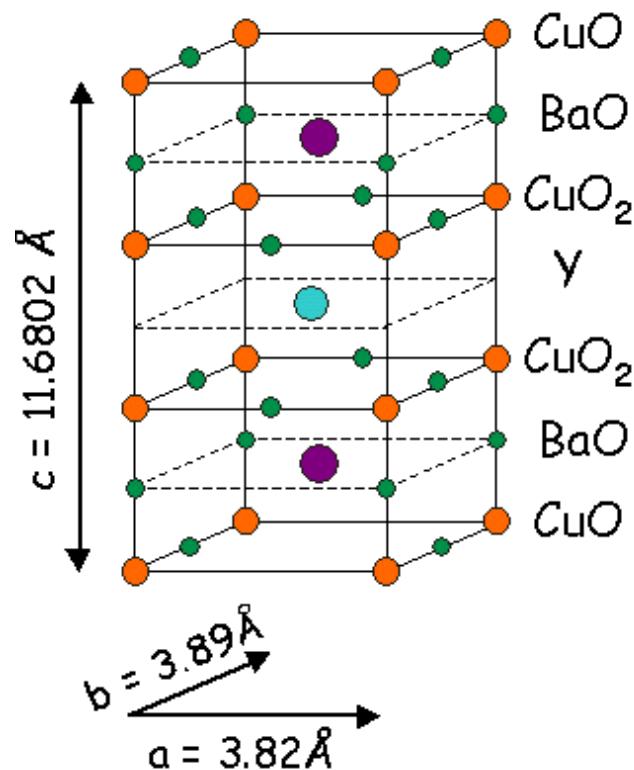
$$n(z, E) dz = p(B, E) dB$$

$$\int_0^z n(\zeta, E) d\zeta = \int_{B(z)}^{\infty} p(\beta, E) d\beta$$

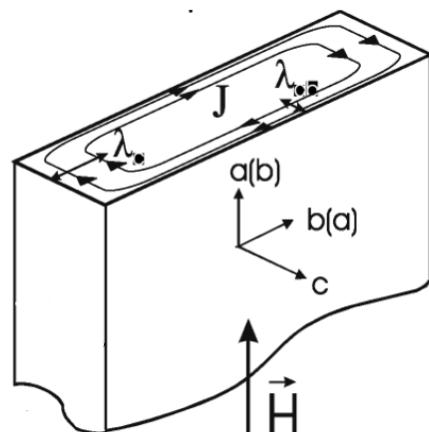
- Magnetic field profile $B(z)$ over nm scale
- Characteristic lengths of the sc λ, ξ

$$\Rightarrow B(z)$$

In plane anisotropy λ_a , λ_b in detwinned $\text{YBa}_2\text{Cu}_3\text{O}_{6.95}$



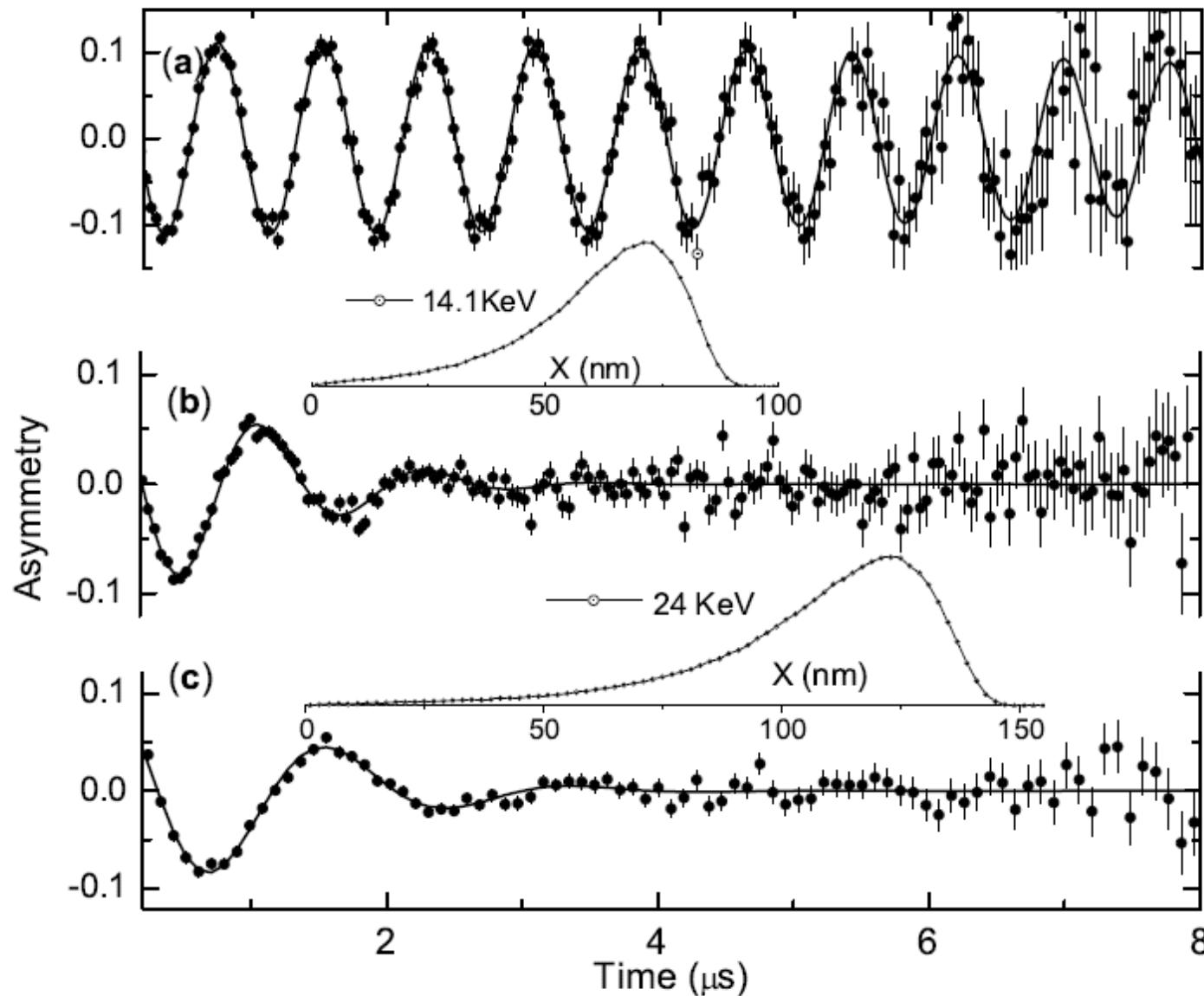
**Detwinned ($>95\%$) $\text{YBa}_2\text{Cu}_3\text{O}_{6.95}$ crystals optimally doped
($T_c = 94.1 \text{ K}$, $\Delta T_c \leq 0.1 \text{ K}$)**



$$\vec{H}_{\text{ext}} \parallel \hat{a}\text{-axis} \rightarrow \lambda_b$$
$$\vec{H}_{\text{ext}} \parallel \hat{b}\text{-axis} \rightarrow \lambda_a$$

samples produced by R. Liang, W. Hardy, D. Bonn,
Univ. of British Columbia

$$\vec{B}_{\text{ext}} = 9.47 \text{ mT} \parallel \hat{a}\text{-axis}$$

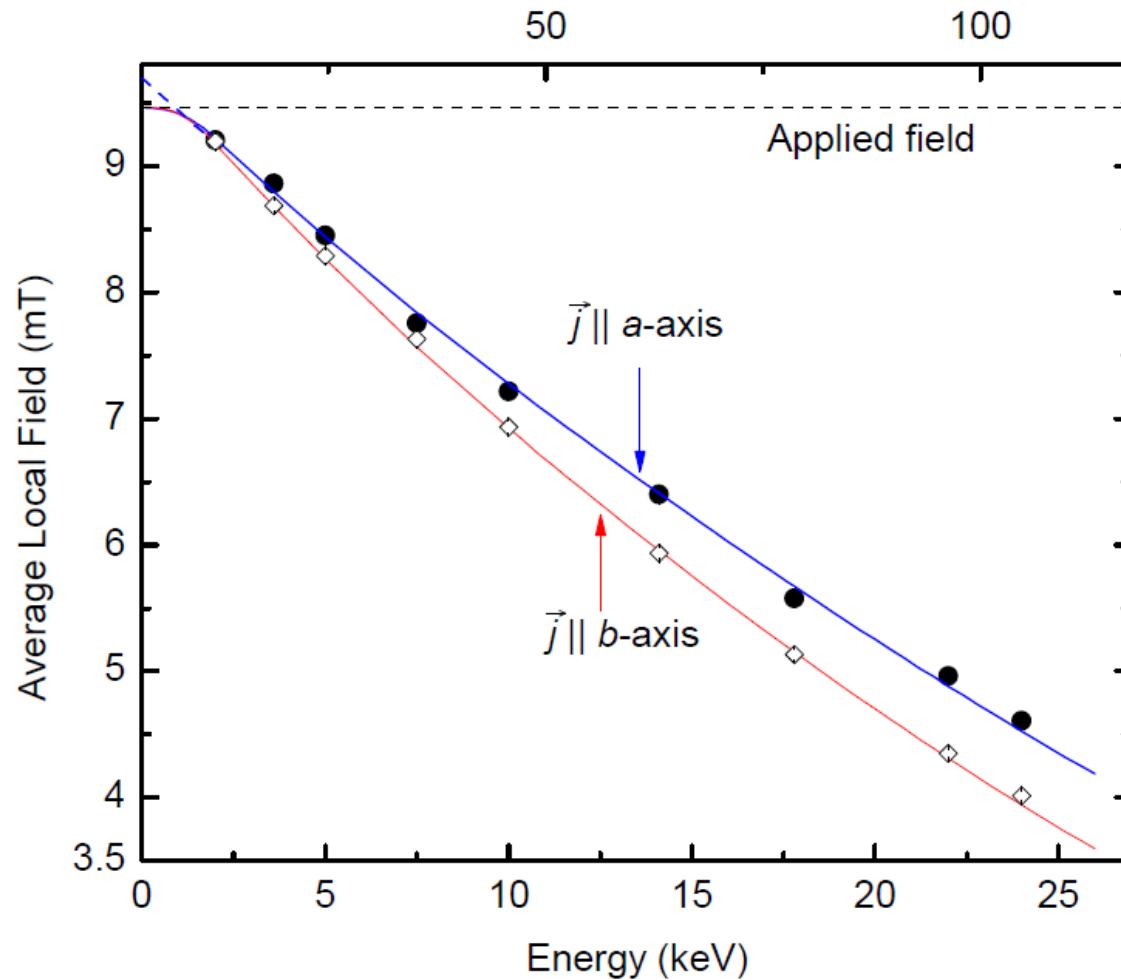


$T = 110 \text{ K}$

$T = 8 \text{ K}$

$$\vec{B}_{\text{ext}} = 9.47 \text{ mT}, T = 8 \text{ K}$$

Mean Depth (nm)



$$B(z) = \begin{cases} B_0 \exp [-(z - d)/\lambda_{a,b}] & , z \geq d \\ B_0 & , z < d, \end{cases}$$

$$d = 10.3(4) \text{ nm}$$

$$\mathcal{A}(t) = A \exp [-\sigma^2 t^2 / 2] \int \rho(z) \cos [\gamma_\mu B(z)t + \phi] \ dz$$

d-wave superconductor

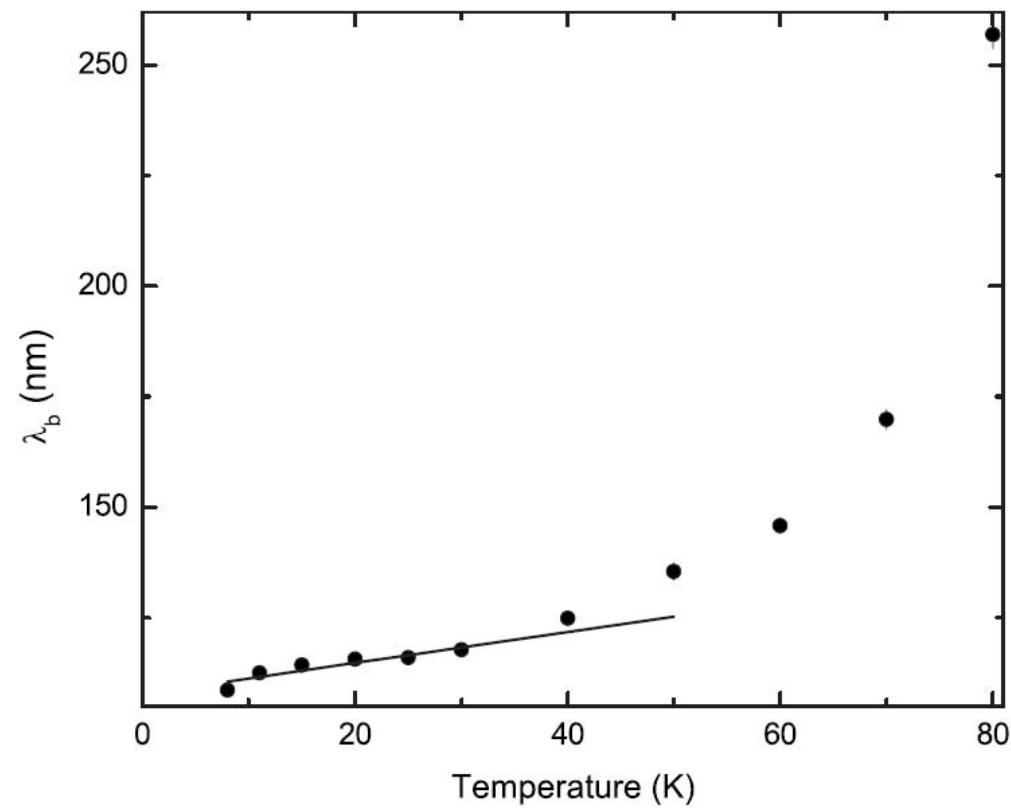
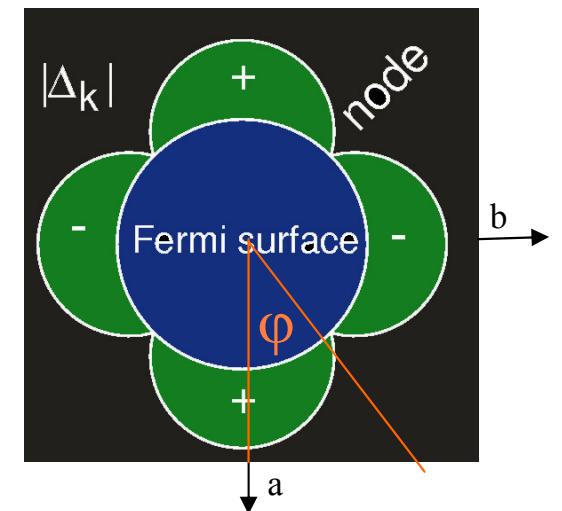


FIG. 3. Temperature dependence of the London penetration depth in an external magnetic field of 9.46 mT applied parallel to the a axis so that the shielding currents are in the b direction and parallel to the CuO chains.

$$\lambda_a = 126 \pm 1.2 \text{ nm}, \lambda_b = 105.5 \pm 1.0 \text{ nm}, \lambda_{ab} = 115.3 \pm 0.8 \text{ nm}, \lambda_a/\lambda_b = 1.19 \pm 0.01$$



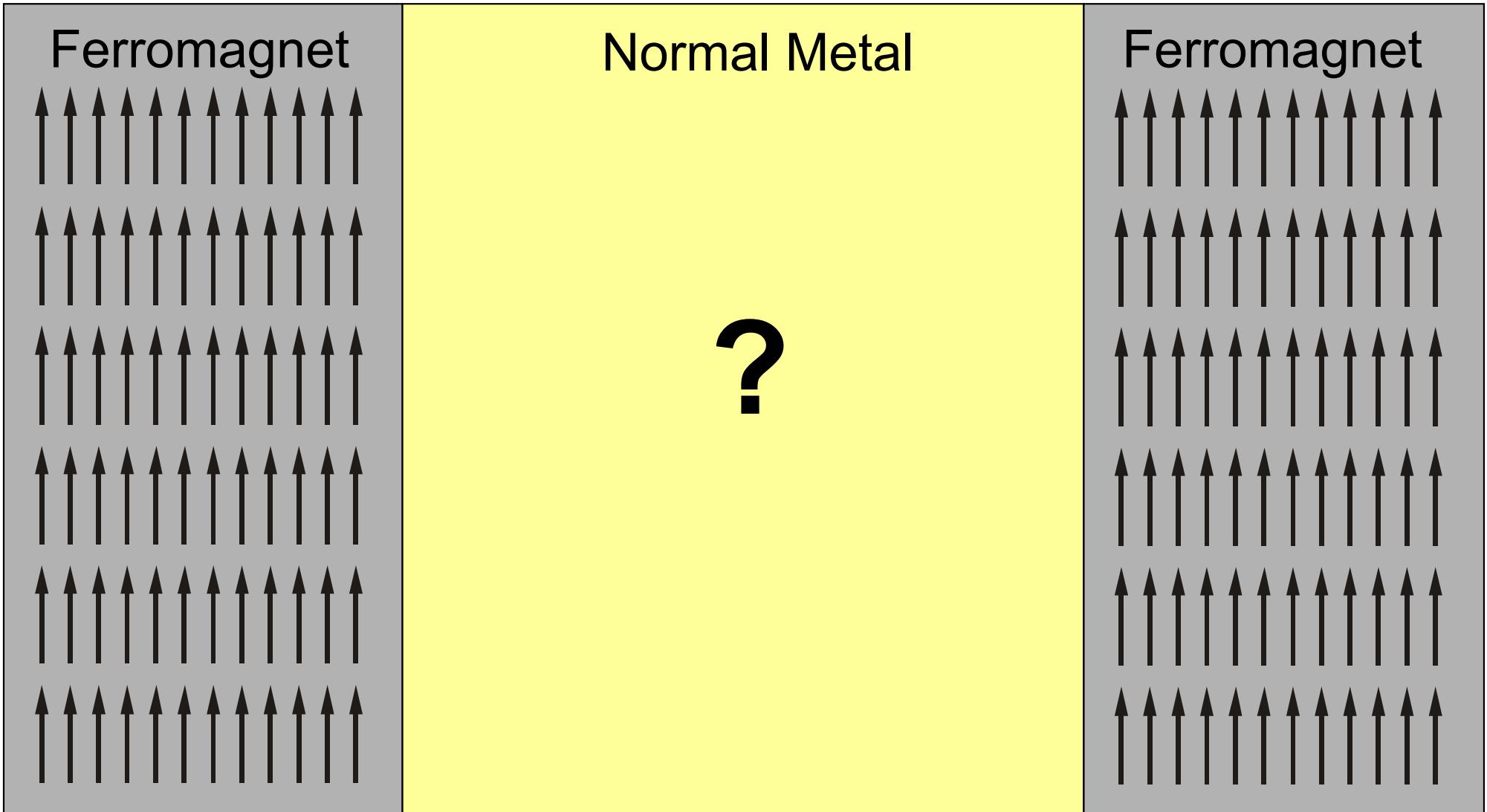
for $\Delta = \Delta(0)\cos(2\varphi)$

for low T:

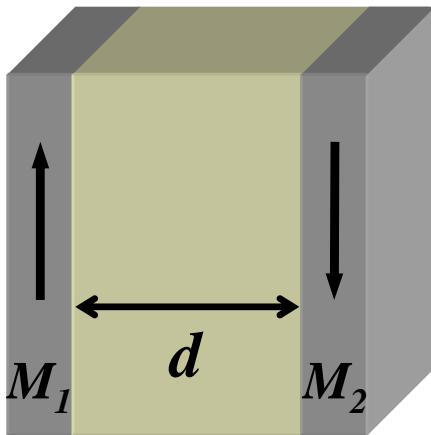
$$\lambda(T) \approx \lambda(0)\left(1 + \frac{\ln 2k_B T}{\Delta(0)}\right)$$

$$\frac{\Delta\lambda}{T} = 0.35(7) \frac{\text{nm}}{\text{K}}$$

Magnetic multilayers (ML)



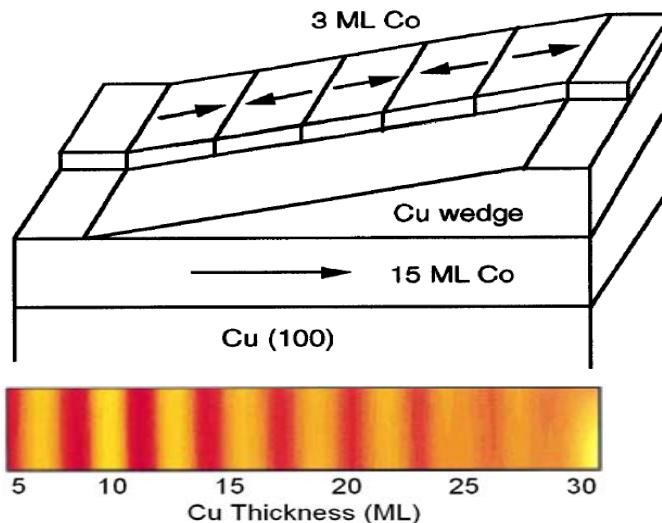
Interlayer exchange coupling in magnetic ML



$$\mathcal{H}_{\text{IEC}} = -J(d) \mathbf{M}_1 \cdot \mathbf{M}_2$$

IEC in trilayers with non-magnetic spacer:

Example: Co/Cu/Co



- IEC oscillates with spacer thickness
(Model: RKKY)

$$J(d) \propto \frac{1}{d^2} \cos(qd + \phi)$$

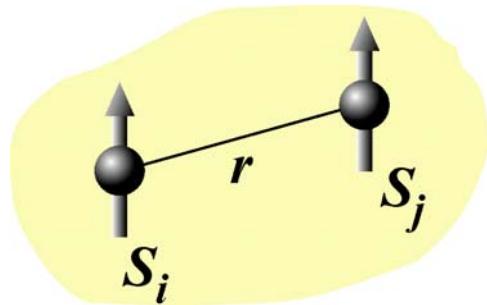
- Different techniques to probe the FM layer
(polarization of secondary electrons,
MOKE, ...)

→ oscillation period, coupling strength

- Muons can probe the spatially varying polarization of the nonmagnetic spacer (Spin Density Wave) mediating the coupling between the FM layers.

RKKY Model

Interaction between two moments via conduction electrons

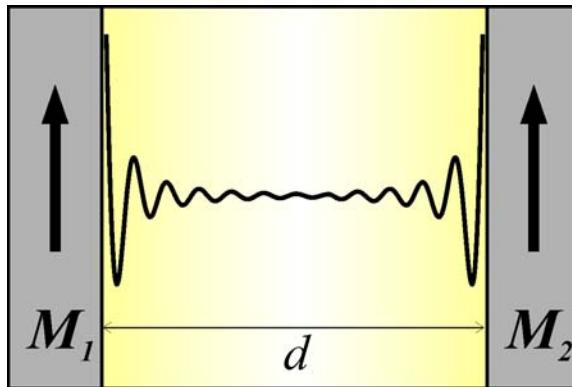


$$\mathcal{H}_{\text{RKKY}} = -J(r) \mathbf{S}_i \cdot \mathbf{S}_j$$

$$J(r) \propto \frac{1}{r^3} \cos(2k_F r + \phi)$$

(leading term for spherical FS)

Interaction between two layers: Integrate over interfaces

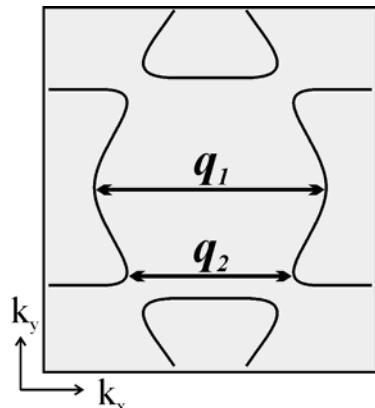


$$J(d) \propto \frac{1}{d^2} \cos(qd + \phi)$$

$$E = -J(d) \mathbf{M}_1 \cdot \mathbf{M}_2$$

In non-spherical Fermi surfaces, oscillations of IEC determined by critical spanning vectors

P. Bruno, C. Chappert, Phys. Rev. Lett. **67**, 1602 (1991)

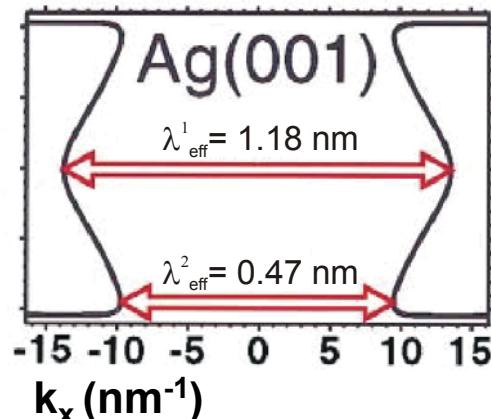


$$\rightarrow J(d) \propto \sum \frac{1}{d^{p_i}} \cos(q_i d + \phi) \quad p_i \leq 2$$

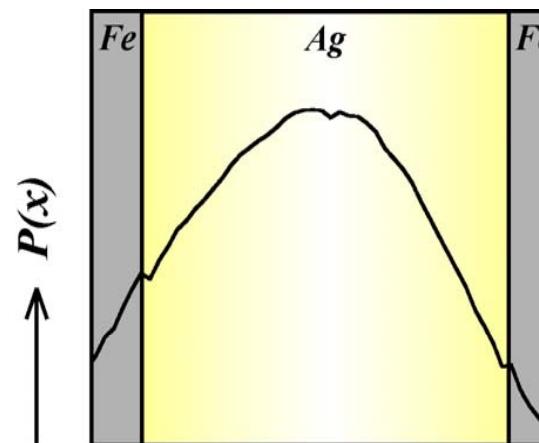
critical spanning vectors Ag: $\lambda_1^{\text{eff}} = 11.8 \text{ \AA}$, $\lambda_2^{\text{eff}} = 4.7 \text{ \AA}$

Oscillating polarization of conduction electrons

Critical spanning vectors in Ag:



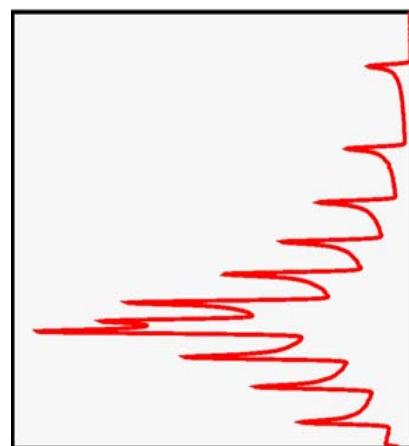
4nm 20nm 4nm



Fe/Ag/Fe

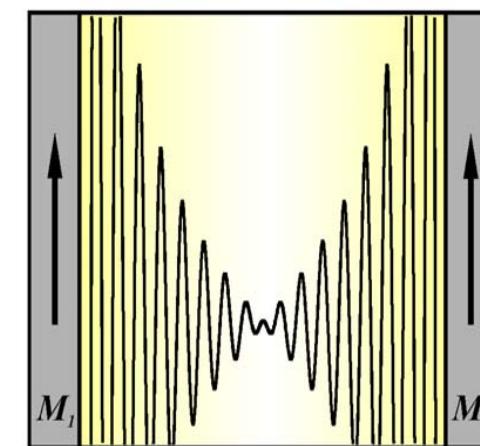
Implantation profile
of 3 keV muons.

$p(B)$ ←



→ B

→ x



We expect an oscillating spin polarization of conduction electrons $P(x)$ in Ag
→ The depth resolution of LE- μ SR cannot resolve the oscillations ($WL \sim 1 \text{ nm}$ or less), but the oscillating behavior if present is reflected in the field distribution $p(B)$ sensed by the muons. Turning points of oscillations should produce side bands to the B_{ext} .

H. Luetkens, J. Korecki, E. Morenzoni, T. Prokscha,
M. Birke, H. Glückler, R. Khasanov, H.-H. Klauss, T.
Slezak, A. Suter, E. M. Forgan, Ch. Niedermayer, and
F. J. Litterst Phys Rev. Lett. **91**, 017204 (2003).

Oscillating polarization of conduction electrons

This is what is observed in the field distribution obtained by Maximum Entropy Fourier analysis.

Results:

- $P(x)$ and IEC oscillate with the same period

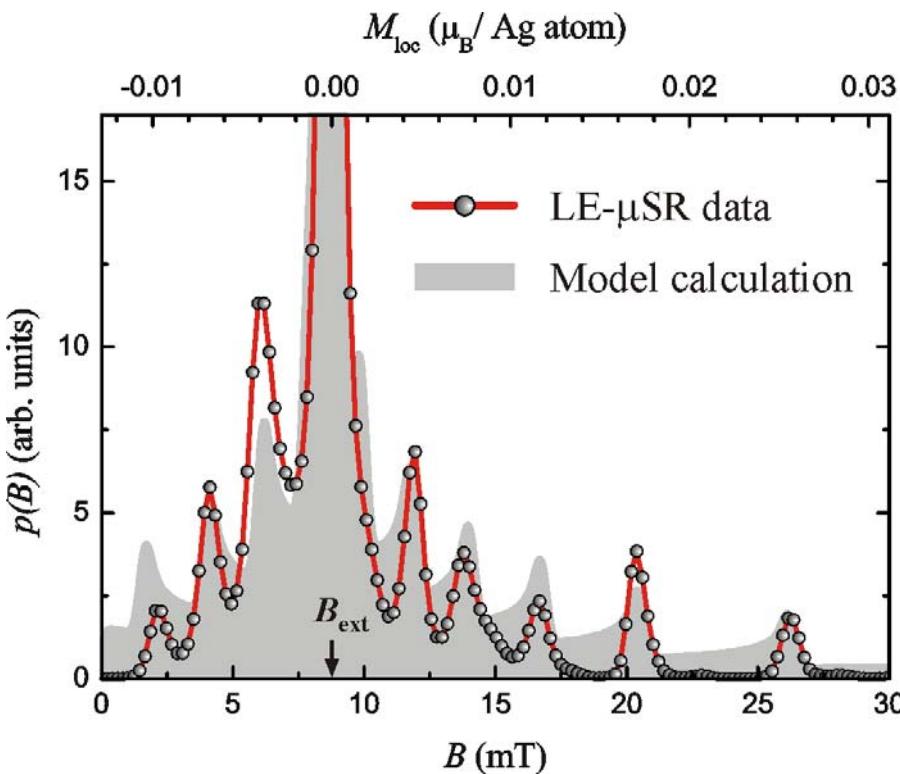
Attenuation of electron spin polarization:

$$P(x) \propto \frac{1}{x^{0.8}}$$

significantly smaller than the one of IEC strength:

$$J(d) \propto \frac{1}{d^2}$$

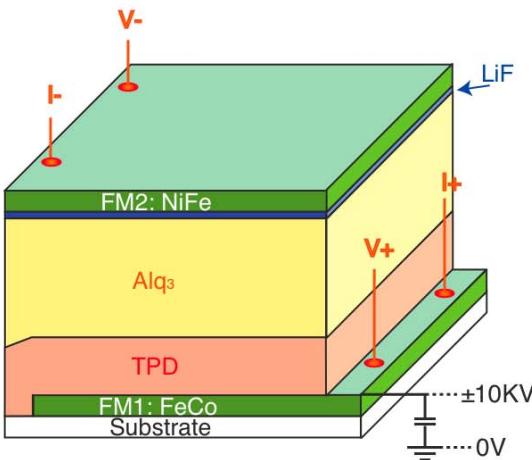
(beyond RKKY: quantum well model)



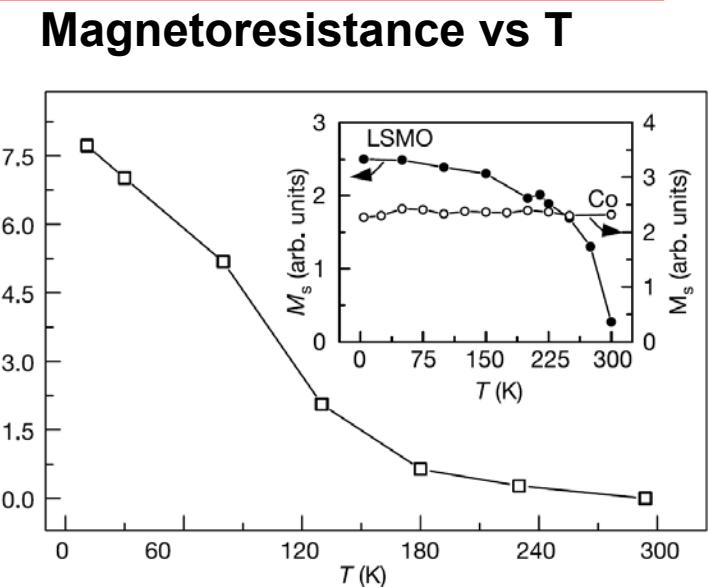
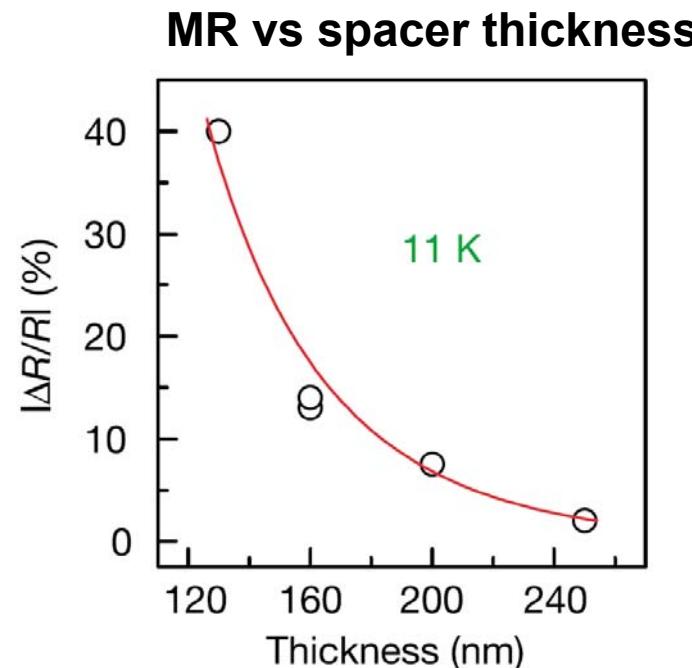
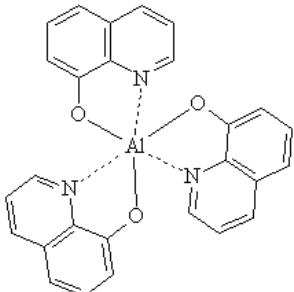
$$J(d) \propto \sum_{i=1}^2 A_i \frac{1}{d^2} \sin(q_{\perp}^i d + \theta_i)$$

$$P(x) = \sum_{i=1}^2 C_i \frac{1}{x^{n_i}} \sin(q_{\perp}^i x + \theta_i)$$

Spin Coherent Transport in Organic Spin Valves

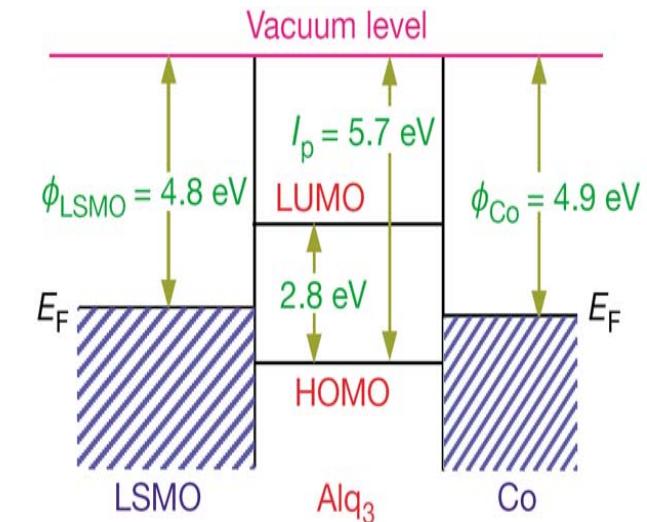


Spacer:
organic semiconductor
Alq₃: C₂₇H₁₈N₃O₃Al

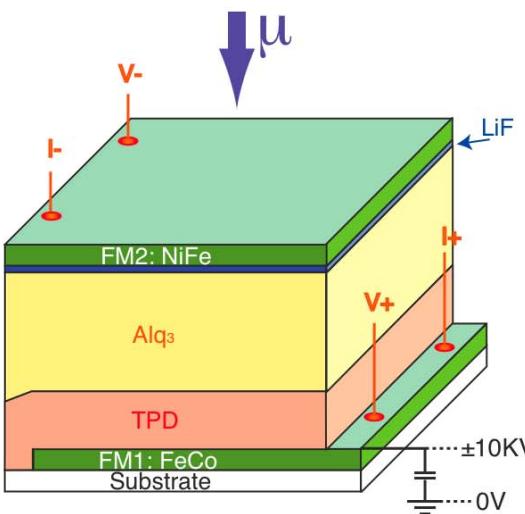


Z.H. Xiong et al., Nature 427, 821 (2004)

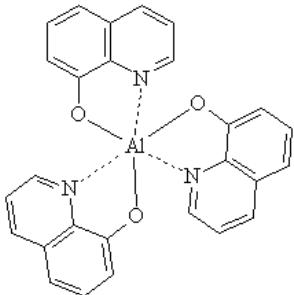
$$MR = \frac{\Delta R}{R} = \frac{R_{AP} - R_P}{R_{AP}}$$



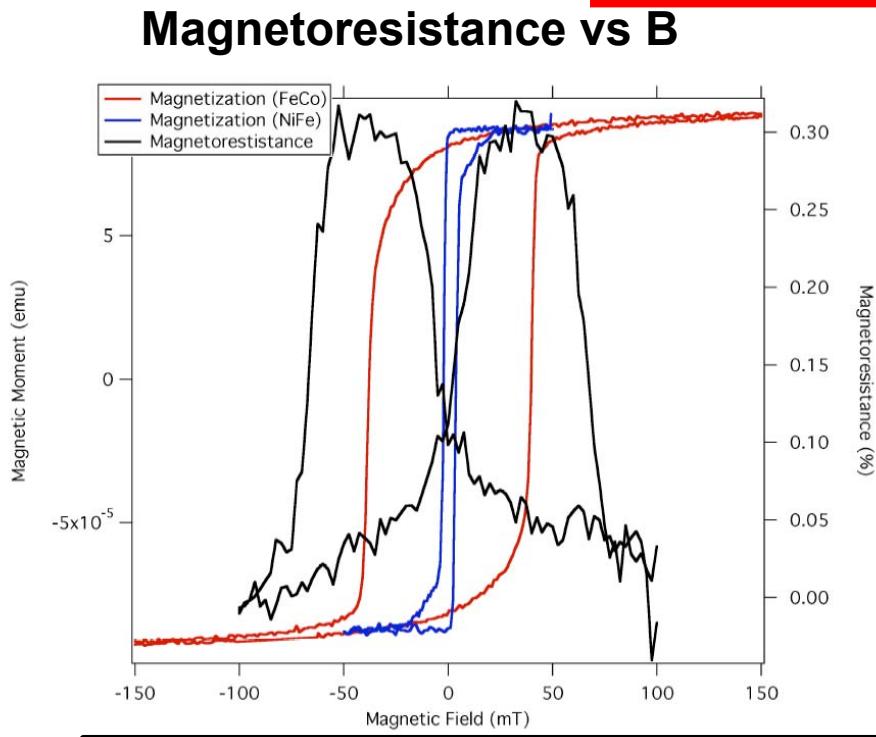
Spin Coherent Transport in Organic Spin Valves



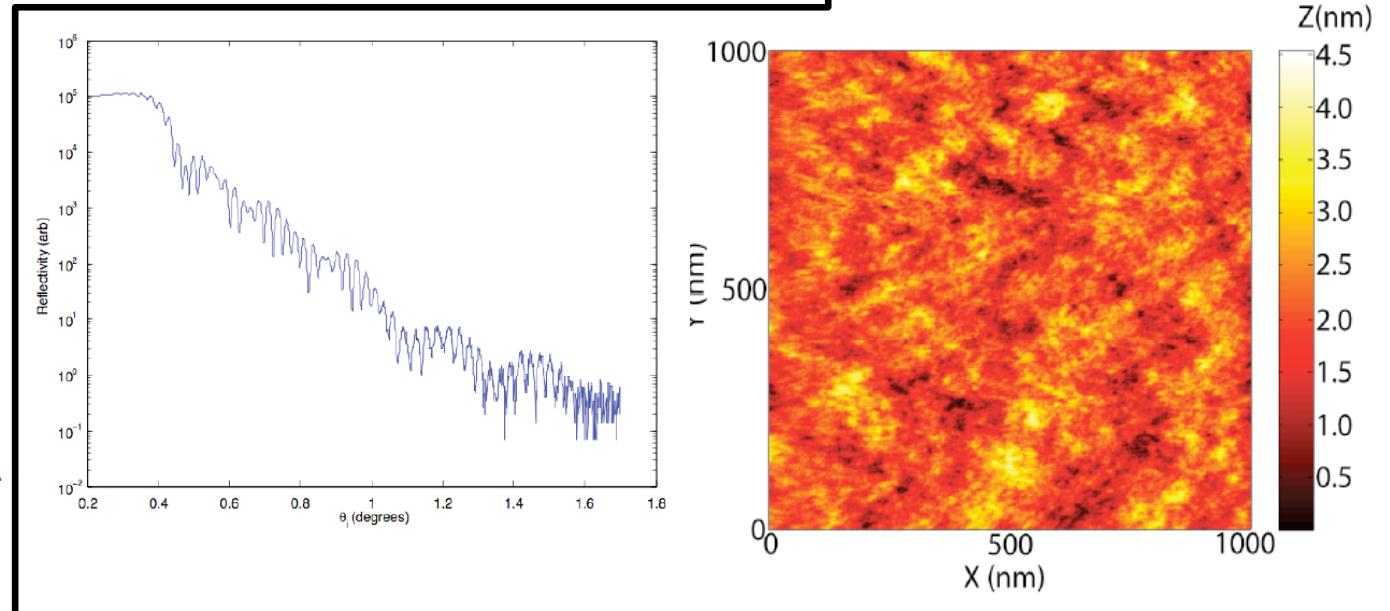
Spacer:
organic semiconductor
Alq₃: $C_{27} H_{18} N_3 O_3 Al$



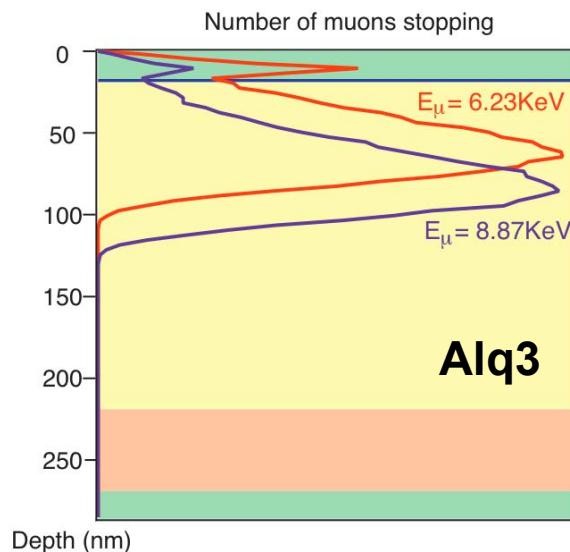
A. J. Drew, J. Hoppler, L. Schulz, F. L. Pratt, P. Desai, P. Shakya, T. Kreouzis, W. P. Gillin, A. Suter, N. A. Morley, V. K. Malik, H. Bouyanif, K. Kim, A. Dubroka, F. Bourqui, C. Bernhard, R. Scheuermann, T. Prokscha, G. Nieuwenhuys, E. Morenzoni, Nature Materials 8, 109-114 (2009)



X-rays, n-reflectivity, AFM
→ very good structural quality, sharp layers and interfaces (rms < 0.5nm)

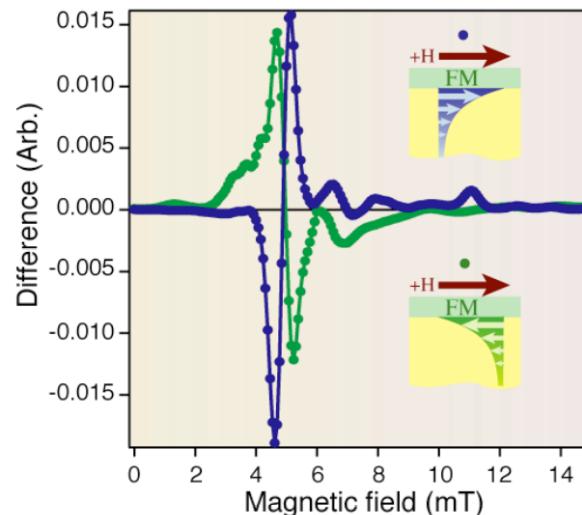


Spin diffusion length in organic spin valve

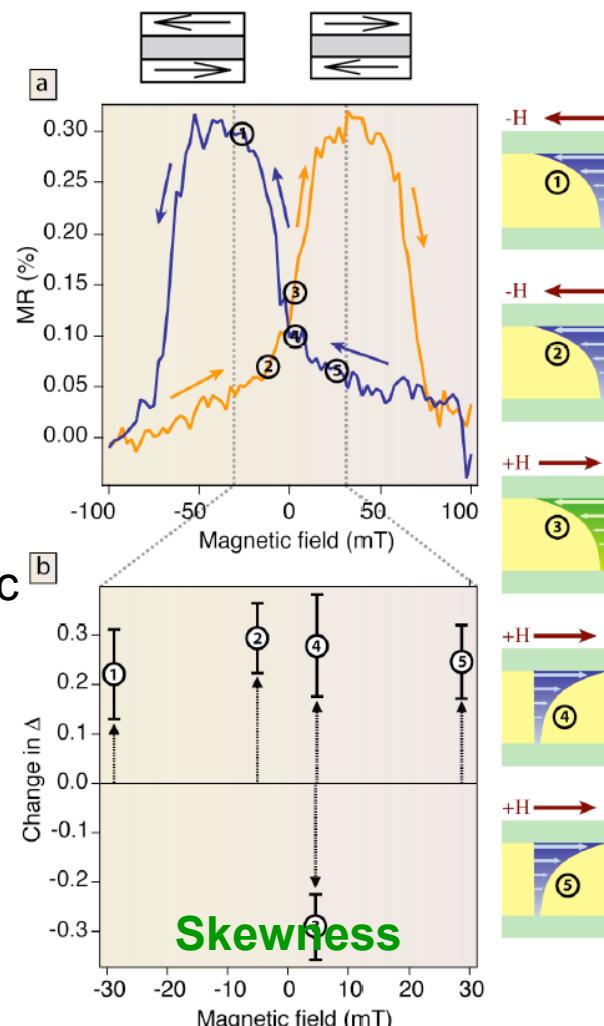


Long coherence time of injected spins $\sim 10^{-5}$ s \rightarrow measurable static field.

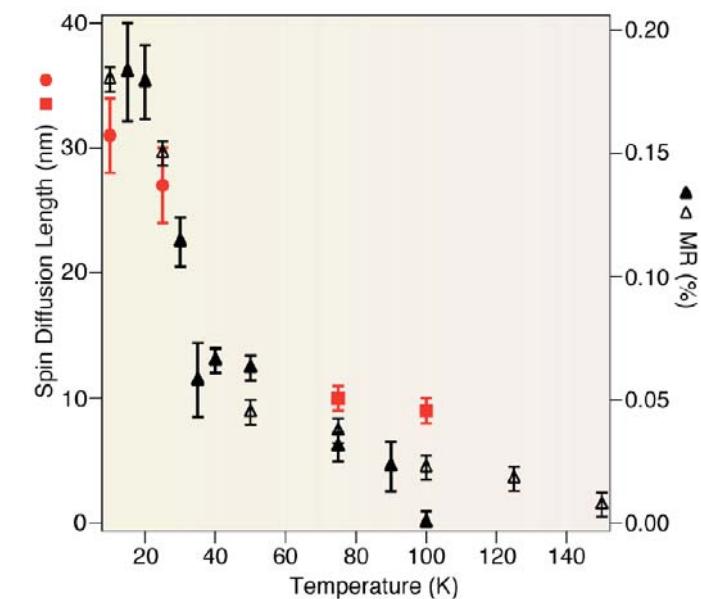
Field distribution: $I_{\text{on}} - I_{\text{off}}$



Magnetoresistance vs B



Spin diffusion length vs T correlates with Magnetoresistance



First direct measurement of spin diffusion length in a working spin valve.

